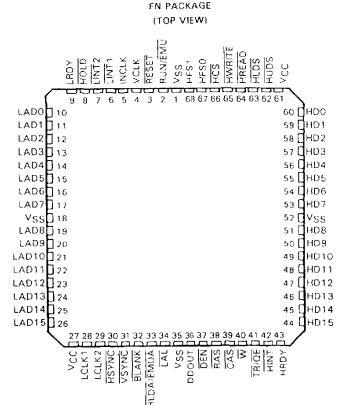
- Instruction Cycle Time: — 132 ns . . . (TMS34010-60) - 160 ns . . . (TM\$34010-50) - 200 ns . . . (TMS34010-40)
- Fully Programmable 32-Bit General-Purpose Processor with 128-Megabyte Address Range
- Pixel Processing, XY Addressing, and Window Checking Built into the Instruction
- Programmable 1, 2, 4, 8, or 16-Bit Pixel Size with 16 Boolean and 6 Arithmetic Pixel Processing Options (Raster-Ops)
- 30 General-Purpose 32-bit Registers and 32-bit Stack Pointer
- 256-Byte LRU On-Chip Instruction Cache
- Direct Interfacing to Both Conventional **DRAM and Multiport Video RAM**
- Dedicated 8/16-Bit Host Processor Interface and HOLD/HLDA Interface
- Programmable CRT Control (HSYNC, VSYNC, BLANK)
- High-Level Language Support
- Full Line of Hardware and Software Development Tools Including a "C" Compiler
- 68-Leaded Packaging (PLCC)
- 5-Volt CMOS Technology

## description

The TMS34010 Graphics System Processor (GSP) is an advanced high-performance CMOS 32-bit microprocessor optimized for graphics display systems. With a built-in instruction cache, the ability to simultaneously access memory and registers, and an instruction set designed specifically for raster graphics operation, the TMS34010 provides user-programmable control of the CRT interface as well as the memory interface (both standard DRAM and multiport video RAM). The 1-gigabit address space is completely bitaddressable on bit boundaries using variable width data fields (1 to 32 bits). Additional graphics addressing modes support 1, 2, 4, 8, and 16-bit wide pixels. The TMS34010 is exceptionally well-supported by graphics software interface standards such as TIGA, MS-Windows, the X Window System, DGIS, and CGI, as well as a full line of hardware and software support tools. Current support is highlighted in the TMS34010 Third Party Reference Guide (literature number SPVB066C).

## architecture

The TMS34010 is a CMOS 32-bit processor with hardware support for graphics operations such as PixBlts traster ops) and curve-drawing algorithms. Also included is a complete set of general-purpose instructions with addressing tuned to support high-level languages. In addition to its ability to address a large external memory range, the TMS34010 contains 30 general-purpose 32-bit registers, a hardware stack pointer



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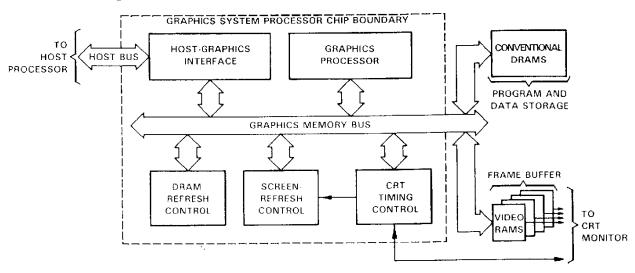
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and a 256-byte instruction cache. On-chip functions include 28 programmable I/O registers that contain CRT control, input/output control, and instruction parameters. The TMS34010 directly interfaces to dynamic RAMs and video RAMs and generates video monitor control signals. It also accommodates a conventional HOLD/HLDA shared access as well as a separate, generalized interface for communicating with any standard host processor.

## pin descriptions

PI!	N I		DECCRIPTION					
NAME	NUMBER	1/0	DESCRIPTION					
			Host Interface Bus Pins					
<del>HCS</del>	66	ĺ	Host chip select					
HDO-HD15	44-51, 53-60	I/O	Host bidirectional data bus					
HESO, HES1	67, 68	1	Host function select					
HINT	42	Ö	Fost interrupt request					
HLDS	63	1	Host lower data select					
HUDS	62		Host upper data select					
HRDY	43	Ö	Host ready					
HREAD	64		Host read strobe					
FWRITE	65		Host write strobe					
	:		Local Bus Interface Pins					
RAS	38	O	Local row-address strobe					
CAS	39	O	Local column-address strobe					
DDOUT	36	O	Local data direction out					
DÉÑ	37	О	Local data enable					
LADO LAD15	10-17, 19 26	FO	Local address/data bus					
LAL	34	O	Local address latched					
LCLK1, 1 CLK2	28, 29	0	Local output clocks					
(INT 1, EIN 2	6, 7	1	Local interrupt request pins					
YCRJ	9	1	Local ready					
TR:OF	41	Э	Local shift register transfer or output enable					
$\overline{W}$	40	0	Local write strobe					
:NCLK	5	1	Input clock					
			Hold and Emulation					
ਜ <b>ਹਿ D</b>	8	I.	Holo request					
RUN/EMU	2	l I	Run/Not emulate					
HLDA/EMUA	33	0	Hold acknowledge or emulate acknowledge					
			Video Timing Signals					
BLANK	32	0	Blanking					
HSYNC	30	1/0	Horizontal sync					
VCLK	4	l	Video clock					
VSYNC	31	EO.	Vertical sync					
			Miscellaneous					
RESET	3	,	Reset					
Ycc	27. 61		Nominal 5-volt power supply					
Vss -	1, 18, 35, 52	[	Ground					

#### system block diagram



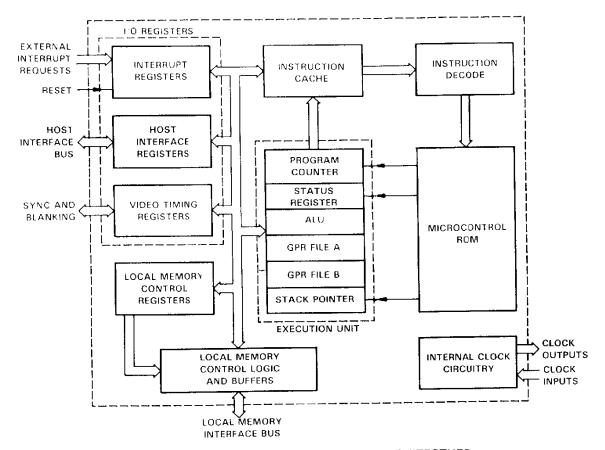


FIGURE 1. TMS34010 INTERNAL ARCHITECTURE

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The TMS34010 provides single-cycle execution of most common integer arithmetic and Boolean operations from its instruction cache. Additionally, the TMS34010 incorporates a hardware barrel shifter that provides a single state bidirectional shift and rotate function for 1 to 32 bits.

A microcoded local memory controller supports pipelined memory write operations of variable-size fields that can be performed in parallel with subsequent instruction execution.

TMS34010 graphics processing hardware supports pixel and pixel-array processing capabilities for both monochrome and color systems that have a variety of pixel sizes. The hardware incorporates two-operand raster operations with Boolean and arithmetic operations, XY addressing, window clipping, window checking operations, 1 to n bits per pixel transforms, transparency, and plane masking. The architecture further supports operations on single pixels (PIXT instructions) or on two-dimensional pixel arrays of arbitrary size (PixBlts).

The TMS34010's flexible graphics processing capabilities allow software-based graphics algorithms without sacrif cing performance. These algorithms include: arbitrary window size, custom incremental curve drawing, and two-operand raster operations.

#### register files

Boolean, arithmetic, byte, and field move instructions operate on data within the TMS34010's general-purpose register files. The TMS34010 contains thirty-one 32-bit registers, including a system stack pointer (SP). The SP is accessible to both Register File A and B as the sixteenth register. Transfers between registers and memory are facilitated via a complete set of field MOVE instructions with selectable field sizes. Transfers between registers are facilitated via the MOVE instruction.

The fifteen general-purpose registers in Register File A are used for high-level language support and assembly language programming. The fifteen registers in Register File B are dedicated to special functions during PixBlts and other pixel operations, but can be used as general-purpose registers at other times.

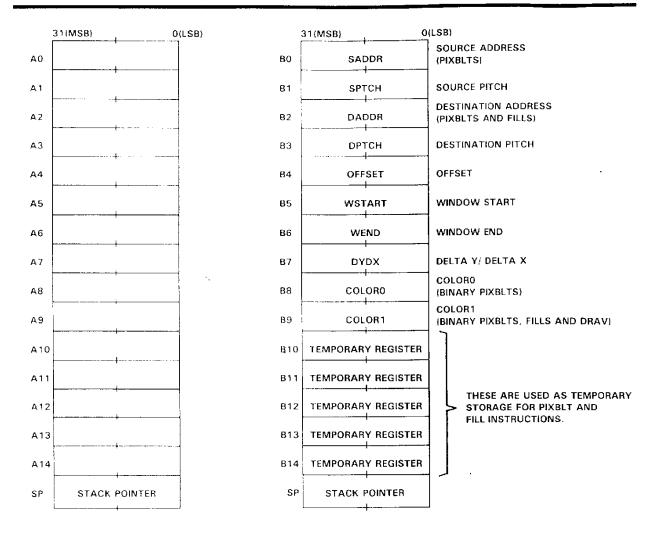


FIGURE 2. REGISTER FILES A AND B

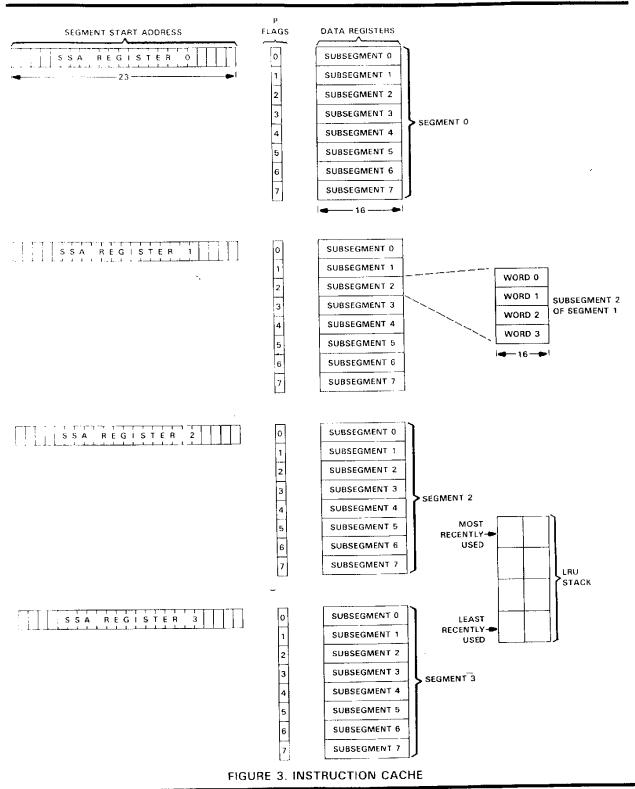
# program counter (PC)

The TMS34010's 32-bit program counter register points to the next instruction-stream word to be fetched. Since instruction words are aligned to 16-bit boundaries, the four LSBs of the PC are always zero.

#### instruction cache

An on-chip instruction cache contains 256 bytes of RAM and provides fast access to instructions. It operates automatically and is transparent to software. The cache is divided into four 64-byte segments. Associated with each segment is a 23-bit segment address register to identify the addresses in memory corresponding to the current contents of the cache segment. Each cache segment is further partitioned into eight subsegments of four words each. Each subsegment has associated with it a present (P) flag to indicate whether the subsegment contains valid data.

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The cache is loaded only when an instruction requested by the TMS34010 is not already contained within the cache. A least-recently-used (LRU) algorithm is used to determine which of the four segments of the cache is overwritten with the new data. For this purpose, an internal four-by-two LRU stack is used to keep track of cache usage.

#### status register

The status register (ST) is a special-purpose 32-bit register dedicated to status codes set by the results of implicit and explicit compare operations and parameters used to specify the length and behavior of fields 0 and 1.

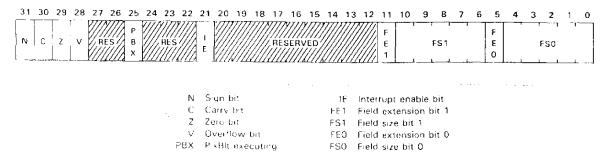


FIGURE 4. STATUS REGISTER

# fields, bytes, pixels, and pixel arrays

A 26-bit address output by the TMS34010 selects a 16-bit word of physical memory; logically, however, the TMS34010 views memory data as fields addressable at the bit level. Primitive data types supported by the TMS34010 include: bytes, pixels, two 1- to 32-bit fields, and user-defined pixel arrays.

Fields 0 and 1 are specified independently to be from 1 to 32 bits in length. Bytes are special 8-bit cases of the field data type, while pixels are 1, 2, 4, 8 or 16 bits in length. In general, fields (including bytes) may start and terminate on arbitrary bit boundaries; pixels must pack evenly into 16-bit words.

## pixel operations

Pixel arrays are two-dimensional data types of user-defined width, height, pixel depth (number of bits per pixel), and pitch (distance between rows). A pixel or pixel array may be accessed by means of either its memory address or its XY coordinates. Transfers of individual pixels or pixel blocks are influenced by the pixel processing, transparency, window checking, plane masking, or corner adjust operations selected.

### I/O registers

The GSP contains an on-chip block of fwenty-eight 16-bit I/O registers mapped into the TMS34010's memory address space. They can be accessed either by the TMS34010's CPU or by the host processor via the host interface. The I/O registers contain control parameters necessary to configure the operation of the following interfaces: interface to host processor (5 I/O registers), interface to local memory (6 registers), video timing and screen refresh functions (15 registers), and externally and internally generated interrupts (2 registers). The I/O registers also furnish status information on these interfaces.



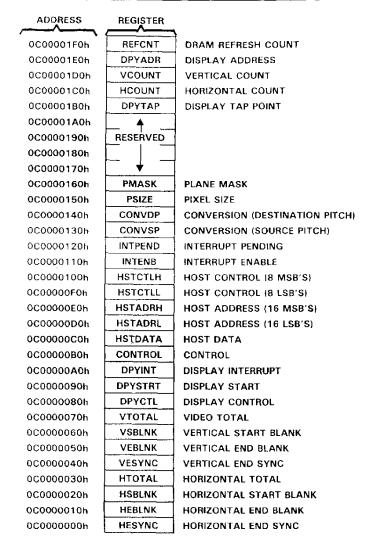


FIGURE 5. I/O REGISTERS

#### host interface registers

The host interface registers are provided for communications between the TMS34010 and the host processor. The registers are mapped into five of the I/O register locations accessible to the TMS34010. These same registers are mapped into four locations in the GSP interface to the host.

One of the registers is devoted to host interface control functions such as the passing of interrupt requests and 3-bit status codes from host to TMS34010 and from TMS34010 to host. Other control functions available to the host processor include flushing the instruction cache, halting the TMS34010, and transmitting a non-maskable interrupt request to the TMS34010.

The remaining host registers are used for block transfers between the TMS34010 and host processor. The host uses these registers to indirectly access blocks within the TMS34010's local memory. Two of the 16-bit registers contain the 32-bit address of the current word location in memory. Another 16-bit register buffers data transferred to and from the memory by the host processor. The host interface can be programmed to automatically increment the pointer address following each transfer to provide the host with rapid access to a block of sequential addresses.

#### memory interface control registers

Six of the I/O registers are dedicated to various local memory interface functions including:

- · Frequency and type of DRAM refresh cycles
- Pixel size
- · Masking (write protection) of individual color planes
- Various pixel access control parameters
  - Window checking mode
     Boolean or arithmetic pixel processing operation
  - Transparency
  - -- PixBlt direction control

#### video timing and screen refresh

Fourteen I/O registers are dedicated to video timing and screen refresh functions. The TMS34010 generates the horizontal sync (HSYNC), vertical sync (VSYNC), and blanking (BLANK) signals used to drive a video monitor in a graphics system. These signals are controlled by means of a set of programmable video timing i C registers and are based on the input video clock, VCLK, VCLK does not have to be synchronous with respect to INCLK, the TMS34010's CPU input clock.

The TMS34010 directly supports multiport video RAMs (VRAMs) by generating the memory-to-register load cycles necessary to refresh the display being shown on the video monitor. The memory locations from which display information is taken, as well as the number of horizontal scan lines displayed between memory-to-register load cycles, are programmable. VRAM tap point addresses are also fully programmable to support horizontal panning.

The TMS34010 supports various screen resolutions and either interlaced or noninterlaced video. The TMS34010 can optionally be programmed to synchronize to externally generated sync signals so that graphics images created by the TMS34010 can be superimposed upon images created externally. The external sync mode can also be used to synchronize the video signals generated by two or more TMS34010 chips in a multiple-TMS34010 graphics system.

#### interrupt interface registers

Two dedicated I/O registers monitor and mask interrupt requests to the TMS34010, including two externally generated interrupts and three internally generated interrupts. An internal interrupt request can be generated on one of the following conditions:

- Window violation: an attempt has been made to write a pixel to a location inside or outside a specified window boundary.
- · Host interrupt: the host processor has set the interrupt request bit in the host control register.
- Display interrupt: a specified line number in the frame has been displayed on the screen.

A nonmaskable interrupt occurs when the host processor sets a particular control bit in the host interface registers. The TMS34010 reset function is controlled by a dedicated pin.



#### memory controller/local memory interface

The memory control or manages the TMS34010's interface to the local memory and automatically performs the bit alignment and masking necessary to access data located at arbitrary bit boundaries within memory. The memory controller operates autonomously with respect to the CPU. It has a "write queue" one field (1 to 32 bits) deep that permits it to complete the memory cycles necessary to insert the field into memory without delaying the execution of subsequent instructions. Only when a second memory operation is required before the memory controller has completed the first operation is the TMS34010 forced to defer instruction execution.

The TMS34010 directly interfaces to all standard dynamic RAMs and, in particular to JEDEC standard 64K and 256K video RAMs such as the TMS4161 and TMS4461 Multiport VRAMs. The TMS34010 memory interface consists of a triple-multiplexed address/data bus plus the associated control signals. Row address, column address, and data are multiplexed over the same address/data lines. DRAM refresh is supported with a variety of modes including  $\overline{CAS}$  before  $\overline{RAS}$  refresh.

## TMS34010 memory map

From the programmer's point of view, the TMS34010 treats data and instructions as residing in the same memory space.

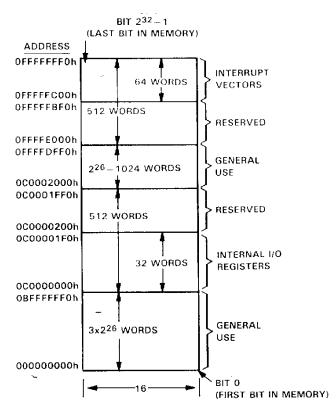


FIGURE 6. MEMORY MAP

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#### instruction set

The TMS34010 instructions fall into three categories. The *graphics instructions* manipulate pixel data, accessed via memory addresses or XY coordinates. They provide support for graphics operations such as array and raster ops, pixel processing, windowing, plane masking, and transparency. The *move instructions* comprehend bit addressing and field operations; they manipulate fields of data using linear addressing for transfer to and from memory and the register file. The TMS34010 *general-purpose instructions* provide a complete set of arithmetic and Boolean operations on the register file as well as general program control and data processing. Partial timing information is provided in the table below. The two values given for jump instructions in the Minimum Cycles column indicate the jump and no-jump conditions, respectively. Full timing information can be obtained in the *TMS34010 User's Guide* (number SPVU001B).

The following abbreviations are used below in the opcodes: S (source register), D (destination register), R (register file select), F (field select), K (constant), M (cross A/B file boundary), Z (draw option), code (jump select code), X (don't care), N (trap select and stack adjust), RS (source register), RD (destination register), xxxx (address displacement), IL (32-bit immediate operand), and IW (16-bit immediate operand).

#### **GRAPHICS INSTRUCTIONS**

SYNTAX	DESCRIPTION	NO. WORDS	MINIMUN		16-BIT	OPCOD	E	;	STA BI	TU: TS	S
				MSB			LSB				
ADDXY Rs, Rd	Add Registers in XY Mode	1	1	1110	000S	SSSR	DDDD	N	С	Z	V
CMPXY Rs, Rd	Compare X and Y Halves of Registers	1	3	1110	0108	SSSR	GDDD	N	С	Z	ν
CPW Rs, Rd	Compare Point to Window	1	1	1110	0115	SSSR	DDDD	_		_	V
CVXYL Rs, Rd	Convert XY Address to Linear Address	1	3	1110	1005	SSSR	dada	_		_	
DRAV Rs, Rd	Draw and Advance	1	t	1111	0118	SSSR	DDDD	_	_	_	V
FILL L	Fill Array with Processed Pixels: Linear	1	†	0000	1111	1100	0000		_		
FILL XY	Fili Array with Processed Pixels: XY	1	‡	0000	1111	1110	0000	_	•	_	V
LINE Z	Line Draw	1	Ť	1101	1111	Z001	1010	_	_	_	٧
MOVX As, Rd	Move X Half of Register	1	1	1110	1108	SSSR	aaaa			-	
MOVY Rs, Rd	Move Y Half of Register	1	1	1110	1118	SSSR	DOOD		_	_	-
PIXBLT B,L	Pixel Block Transfer: Binary to Linear	1	t	0000	1111	1000	0000			_	
PIXBLT B, XY	Pixel Block Transfer and Expand: Binary to XY	1	†	0000	1111	1010	0000			_	V
PIXBLT L.L	Pixel Block Transfer: Linear to Linear	1	†	0000	1111	0000	0000	_		_	
PIXBLT L,XY	Pixel Block Transfer: Linear to XY	1	t	0000	1111	0010	0000	_	_	_	٧
PIXBLT XY, L	Pixel Block Transfer: XY to Linear	1	†	0000	1111	0100	0000	_	_	_	
PIXBLT XY,XY	Pixel Block Transfer: XY to XY	1	†	0000	1111	0110	0000	_		_	V
PIXT Rs, *Rd	Pixel Transfer: Register to Indirect	1	†	1111	100S	SSSR	DDDD	-	_	_	
PIXT Rs, *Rd.XY	Pixel Transfer: Register to Indirect XY	1	t	1111	000S	SSSR	DDDD	~	_	-	٧
PIXT *Rs, Rd	Pixel Transfer: Indirect to Register	1	4	1111	101S	SSSR	DDDD		_	_	-
PIXT *Rs,*Rd	Pixel Transfer: Indirect to Indirect	1	†	1111	1108	SSSR	DDDD	_	_	_	_
PIXT *Rs.XY. Rd	Pixel Transfer: Indirect XY to Register	1	6	1111	0015	SSSR	DDDD	_	_		~
PIXT *Rs.XY, *Rd XY	Pixel Transfer: Indirect XY to Indirect XY	1	†	1111	0108	SSSR	DDDD	_		_	V
SUBXY Rs.Rd	Subtract Registers in XY Mode	1	1	1110	0015	SSSR	DDDD	Ν	С	Z	٧

<sup>\*</sup>Number of cycles depends on pixel size an/or pixel array size and graphics option selected. See TMS34010 User's Guide (SPVU001B)

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# MOVE INSTRUCTIONS

		NO.	MINIMUM		STATUS
SYNTAX	DESCRIPTION	WORDS	CYCLES	16-BIT OPCODE  MSB LSB	BITS
MOVB Rs.*Rd	Maria Distance Description to 1. Hours	1	1	1000 110S SSSR DDDD	
MOVB *Rs, Rd	Move Byte: Register to Indirect	1	t t	1000 1115 SSSR DDDD	
MOVB *Rs, *Rd	Move Byte: Indirect to Register  Move Byte: Indirect to Indirect	1	1	1001 110S SSSR DDDD	
MOV5 As, "Rd(offset)	"	2	t t	1010 1105 SSSR DDDD	
MOVB *Rs; offset) Rd	Make Byte: Register to Indirect with offset.	2	t	1010 1115 SSSR DDDD	
MOVB "Risothsett, "Rotoffset)	Move Byte: Indirect with offset, to Register	2	·	1010 1113 33311 0000	14 – 2 0
VOVE ASSORBET, ROTOTISETS	Move Byte: ind. with offset, to Ind.	3	1	1011 110S SSSR DDDD	
MOVB Rs.@Dadoress	with offset	3	1	0000 0101 111R SSSS	
MCVB @Saddress.Rc	Move Byte: Register to Absolute	3	†	0000 0101 111R DDDD	
MOVE @Saddress,@Daddress	Move Byte: Absolute to Register  Move Byte: Absolute to Absolute	5 5	t	0000 0011 0100 0000	
MCVF Rs Rd	Move Register to Register	1	1	0100 11MS SSSR DDDD	
MOVE Rs, *Rd,F	Move Field: Register to Indirect	1	†	1000 00FS SSSR DDDD	_
MOVE Rs. 1Rd,1	Move Field: Register to Indirect (pre-dec)	1	t	1010 00FS SSSR DDDD	
MOVE Rs. *Rd + F	Move Field: Register to Indirect (pre-dec)	1	t	1001 00FS SSSR DDDD	
MOVE 1Rs Rd,F	Move Field: Indirect to Register	1	†	1000 01FS SSSR DDDD	
MOVE *Rs,Rd,F	Move Field: Indirect to Register	1	t	1010 01FS SSSR DDDD	
MOVE RsRd,F	Move Field: Indirect (post-inc) to Register	1	t	1001 01FS SSSR DDDD	
MOVE 'Rs 'Rd F	Move Field: Indirect to Indirect  Move Field: Indirect to Indirect	1	t	1000 10FS SSSR DDDD	
MOVE 18s - 18d.F	Move Field Ind. (pre-dec) to Ind. (pre-dec)	1	1	1010 10FS SSSR DDDD	
MOVE TRS - TRd - F	Move Field: Ind. (post-inc) to Ind. (post-inc)	1	t	1001 10FS SSSR DODD	
MOVE Rs * Paraffsett, F	Move Field: Register to Indirect with offset.	2	t	1011 OOFS SSSR DDDD	
MOVE "Rejotfset).Rd,F	Move Field: Indirect with offset, to Register	2	t	1011 OIFS SSSR DDDD	
MOVE *Rs(offset), *Rd - ,F	Move Field: Ind. with offset, to Ind.	•.			
11107 12 111107	(post-inc)	2	t	1101 OOFS SSSR DDDD	)
MOVE *Rstoffset) *Rd(offset),F	Move Field: Ind. with offset, to Ind.	-		,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	
11.012 11.01.000	with offset.	3	t	1011 10FS SSSR DDDD	)
MOVE Rs,@Daddress,F	Move Field: Register to Absolute	3	t	0000 01F1 100R SSSS	
MOVE @Saddress,Rd,F	Move Field: Absolute to Register	3	t	0000 01F1 101R DDDD	N - Z O
MOVE @Saddress.*Rd+,F	Move Field: Absolute to Indirect (post-inc)	3	t	1101 01F0 000R DDDD	)
MOVE @Saodress.@Daddress F	Move Field: Absolute to Absolute	5	t	0000 01F1 1100 0000	

<sup>\*</sup>Number of cycles depends on field size and alignment. See TMS34010 User's Guide (SPVU001B).

# **GENERAL INSTRUCTIONS**

PVNITA V		NO.	MINIMUM				STATUS
SYNTAX	DESCRIPTION	WORDS	CYCLES		16 BIT	OPCODE	BITS
ADC D4				MSB		LSB	
ABS Rd	Store Absolute Value	1	1	0000		100R DDDD	N - Z 0
AOD Rs,Rd	Add Registers	1	1	0100		SSSR DDDD	N C Z V
ADDC Rs,Rd	Add Register with Carry	1	1	0100	0015	SSSR DDDD	N C Z V
ADD: IW.Rd	Add Immediate (16 Bits)	2	2	0000	1011	OOOR DDDD	N C Z V
ADDI IL,Rd	Add Immediate (32 Bits)	3	3	0000	1011	001R DDDD	N C Z V
ADDK K,Rd	Add Constant (5 Bits)	1	1	0001	OOKK	KKKR DDDD	NCZV
AND Rs,Rd	AND Registers	1	1	0101	0008	SSSR DDDD	Z -
ANDI IL.Rd	AND Immediate (32 Bits)	3	3	0000	1011	100R DDDD	Z -
ANDN Rs,Rd	AND Register with Complement	1	1	0101	0015	SSSR DDDD	Z -
ANDNI IL,Rd	AND Not Immediate (32 Bits)	3	3	0000	1011	100R DDDD	Z -
BTST K.Rd	Test Register Bit - Constant	1	1	0001	11KK	KKKR DDDD	Z
BTST Rs.Rd	Test Register Bit Register	1	2	0100	1015	SSSR DDDD	Z -
CLR Rd	Clear Register	1	1	0101	011D	DDDR DDDD	
CLRC	Clear Carry	1	1	0000	0011	0010 0000	- 0
CMP Rs.Rd	Compare Registers	1	1	0100		SSSR DDDD	NCZV
CMPLIW,Rd	Compare Immediate (16 Bits)	2	2	0000		O1OR DDDD	NCZV
CMPLIL,Rd	Compare Immediate (32 Bits)	3	3	0000	1011	011R DDDD	NCZV
DEC Rd	Decrement Register	1	1	0001		001R DDDD	
DINT	Disable Interrupts	1	3	0000		0110 0000	
DIVS Rs,Rd	Divide Registers Signed	1	40	0101		SSSR DDDD	N - Z V
DiVU Rs,Rd	Divide Registers Unsigned	1	37	0101		SSSR DDDD	Z V
EINT	Enable Interrupts	1	3	0000		0110 0000	
EXGF Rd,F	Exchange Field Size	1	1	1101		OOOR DDDD	
INC Rd	Increment Register	1	1	0001		001R DDDD	
LMO Rs.Rd	Leftmost One	1	1			SSSR DDDD	Z -
MMFM Rs, Register List	Move Multiple Registers from Memory	2	Ť			101R DDDD	
MMTM Rd,Register List	Move Multiple Registers to Memory	2	t	0000		100R DDDD	
MODS Rs.Rd	Modulus Signed	1	40			SSSR DDDD	N Z V
MODU Rs,Rd	Modulus Unsigned	1	35			SSSR DDDD	Z V
MOVI IW, Rd	Move Immediate (16 Bits)	2	2			110R DDDD	N - Z 0
MOVI IL,Rd	Move_Immediate (32 Bits)	3	3	0000		111R DDDD	N - Z = 0
MOVK K,Rd	Move Constant (5 Bits)	1	1			KKKA DDDD	- <b>-</b>
MPYS Rs,Rd	Multiply Registers (Signed)	1	5 + FS1			SSSR DDDD	N - Z -
	Worth Garters (Signed)	'	_	0101	1103	333K DDDD	N - Z -
MPYU Rs,Rd	Multiply Registers (Unsigned)	1	5 + FS1 2	0101	1115	SSSR DDDD	– - Z ···
NEG Rd	Negate Register	1	1	0000	0011	101R DDDD	NCZV
NEGB Rd	Negate Register with Borrow	1	1	0000	0011	110R DDDD	NCZV
NOP	No operation	1	1			0000 0000	
NOT Rd	Complement Register	1	1			111R DDDD	Z -
OR Rs,Rd	OR Registers	1	1			SSSR DDDD	
ORI IL,Rd	OR Immediate (32 bits)	3	3			101R DDDD	
RL K,Rd	Rotate Left - Constant	1	1			KKKR DDDD	
RL Rs,Rd	Rotate Left - Register	1	1			SSSR DDDD	
SETC	Set Carry	1	1			1110 0000	
SETF FS,FE,F	Set Field Parameters	1	1,2			O1FS SSSS	
SEXT Rd,F	Sign Extend to Long	1	3			OOOR DDDD	
	· p	•	-				_

<sup>&</sup>lt;sup>1</sup>Number of cycles depends on number of registers in list and stack alignment. See TMS34010 User's Guide (SPVU001B).

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		NO.	MINIMUM	1				5	STA	TUS	5
SYNTAX	DESCRIPTION	WORDS	CYCLES	•	16-BIT	OPCOD	E		BI	TS	
				MSB			LSB				
SLA K.Rd	Shift Left Arithmetic - Constant	1	3	0010	OOKK	KKKR	DDDD	Ν	С	Z	٧
SLA Rs,Rd	Shift Left Arithmetic Register	1	3	0110	000S	SSSR	DDDD	N	С	Z	V
SEL K,Rd	Shift Left Logical - Constant	1	1	0010	01KK	KKKR	DDDD	_	C	Z	_
Sul Rs,Rc	Shift Left Logical - Register	1	1	0110	001S	SSSR	DDDD		С	Z	-
SRA KJRa	Shift Right Anthmetic Constant	1	1	0010	10KK	KKKR	DDDD	Ν	C	Z	٠.
SRA Rs.Ra	Shift Right Arithmetic Register	1	1	0110	0108	SSSR	adda	Ν	C	Z	_
SRL K Sa	Shift Right Logical - Constant	1	1	0010	11KK	KKKR	ODDO		C	Z.	
SRL Rs.Rd	Shift Right Logical Register	1	1	0110	0118	SSSR	DDDD	_	C	Z	_
SUB Hs Ra	Subtract Registers	1	1	0100	0105	SSSR	DDDD	Ν	C	2	V
SUBB Rs Rd	Subtract Registers with Borrow	1	1	0100	0115	SSSR	DDDD	N	С	Z	V
SUBI IW, Rd	Subtract Immediate (16 Bits)	2	2	0000	1011	111R	DDDD	Ν	С	Z	V
SUBI IL,Rd	Subtract Immediate (32 Bits)	3	3	0000	1101	000R	DDDD	Ν	С	Z	V
SUBK K.Rd	Subtract Immediate (5 Bits)	1	1	0001	01KK	KKKR	adaa	Ν	С	Z	V
XOR Rs,Rd	Exclusively OR Registers	1	1	0101	011S	SSSR	aaaa	_	_	Z	
XORI IL.Rd	Exclusively OR Immediate Value (32 Bits)	3	3	0000	1011	110D	DDDD	_	_	Z	_
ZEXT Rd,F	Zero Extend to Long	1	1	0000	01F1	001R	DDDD			Z	

# PROGRAM CONTROL AND CONTEXT SWITCHING

		NO.	MINIMUN	4				5	STA	TU	s
SYNTAX	DESCRIPTION	WORDS	CYCLES		16-BIT	OPCOD	E		ы	TS	
				MSB			LSB				
CALL Rs	Call Subroutine Indirect	1	6	0000	1001	001R	DDDD	_			_
CALLA Address	Call Subroutine Absolute	3	6	0000	1101	0101	1111		~~	_	_
CALLR Address	Call Subroutine Relative	2	5	0000	1101	0011	1111		-	_	
DSJ Rd.Address	Decrement Register and Skip Jump	2	3,2	0000	1101	100R	DDDD	_	_	_	
DSJEQ Rd.Address	Conditionally Decrement Register and Skip Junip	2	3,2	0000	1101	101R	DDDD	_	-	-	_
DSJNE Rd, Address	Conditionally Decrement Register and Skip Jump	2	3,2	0000	1101	110R	DDDD		~		_
DSJS Rd,Address	Decrement Register and Skip Jump - Short	1	2,3	0011	1Dxx	xxxR	DDDD	_			
EMU	Initiate Emulation	1	6	0000	0001	0000	0000			_	_
EXGPC Rd	Exchange Program Counter with Register	1	2	0000	0001	001R	DDDD		_	_	-
GETPC Rd	Get Program Counter into Register	1	1	0000	0001	010R	DDDD		-		
GETST Ro	Get Status Register into Register	1	1	0000	0001	100R	DDDD		-		
BAdd Address	Jump Absolute Conditional	3	3,4	1100	code	1000	0000	_			
JRcc Address	Jump Relative Conditional	2	3,2	1100	code	0000	0000	_	_	_	_
JRcc Address	Jump Relative Conditional - Short	1	2,1	1100	code	xxxx	xxxx	-	*		
JUMP Rs	Jump Indirect	1	2	0000	0001	011R	DDDD			_	
POPST	Pop Status Register from Stack	1	8	0000	0001	1100	0000	_	_	_	_
PUSHST	Push Status Register onto Stack	1	2	0000	0001	1110	0000			_	
PUTST Rs	Copy Register into Status	1	3	0000	0001	101R	DDDD	N	С	Z	٧
RETI	Return from Interrupt	1	11	0000	1001	0100	0000	Ν	С	Z	٧
RETS (N)	Return from Subroutine	1	7	0000	1001	011N	NNNN		_	_	-
REV Rd	Get Revision Number	1	1	0000	0000	001R	DDDD		_	_	
TRAP N	Software Interrupt	1	16	0000	1001	000N	NNNN	0	0	0	0

<sup>\*</sup>Where two numbers appear, the first number assumes that the jump is taken, and the second assumes that the jump is not taken.

hardware and software support for the TMS34010

#### PART NUMBER

#### DESCRIPTION

#### TMS340SDK-PC

#### TMS340 Software Developer's Kit

The SDK meets the needs of those developers of TIGA-compatible software applications and drivers who must develop custom extensions to the standard TIGA graphics library. Included in this package are the TMS340 Family Code Generation Tools, TIGA Software Developer's Package, TMS340 Family Graphics Library, and TMS340 C Source Debugger. The software runs on the IBM PC-AT and compatible MS-DOS machines.

TMS340 Family Code Generation Tools: Includes a C compiler, TMS340 assembler, linker, archiver, and ROM utility. These software tools generate code for both the TMS34010 and TMS34020. TMS34082 support is provided.

TIGA Software Developer's Package: Provides the utilities needed by the developer to produce TIGA drivers for software applications.

TMS340 Family Graphics Library: Provides source and object code for the standard TIGA graphics functions. This package provides a convenient starting point for those developing TMS34010 and TMS34020 code for non-TIGA environments. This product replaces two older products: the TMS34010 Math/Graphics Function Library and the TMS34010 Font Library.

TMS340 Family C Source Debugger: Provides symbolic and high-level language facilities for debugging code for the TMS34010 and TMS34020 written in both C and TMS340 assembly language. Runs on any TIGA board.

## TMS340SPK-PC

## TIGA Software Porting Kit

The SPK meets the needs of OEM equipment makers who are porting the TIGA software interface to their TMS34010- and TMS34020-based hardware products. This package contains the complete source code necessary to build and run TIGA on a TMS340-based board. The SPK also contains the TIGA driver for MS Windows 3.0, and the complete TMS340 Software Developer's Kit (described above).

## SPVZ071

## TIGA Driver Developer's Kit

The TIGA DDK meets the needs of those developers of TIGA-compatible software applications and drivers who do not need to develop custom extensions to the standard TIGA graphics library. Included in this package are the TIGA application interface libraries, example programs, and other TIGA-related files and information. All that is needed in addition to the DDK is an IBM-compatible PC, a TIGA board, and a C compiler for MS-DOS machines.

TMDS3442203018	
TMDS3442213018	
TMDS3442553008	

TMS340 Family C Compiler for VAX/VMS TMS340 Family C Compiler for VAX TMS340 Family C Compiler for SUN

TMDSTDB10 TMDS3469910000 TMDS3469981000 TMS34010 TIGA Development Board TMS34010 XDS/22 Realtime Hardware Emulator, U.S. TMS34010 XDS/22 Realtime Hardware Emulator, Europe

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#### reset

Reset puts the TMS34010 into a known initial state. It is entered when the input signal at the RESET pin is asserted low. RESET must remain active low for a minimum of 40 local clock (LCLK1 and LCLK2) periods to ensure that the TMS34010 has sufficient time to establish its initial internal state.

While RESET remains asserted, all outputs are in a known state, no DRAM-refresh cycles take place, and no screen-refresh cycles are performed.

At the low-to-high transition of the RESET signal, the state of the HCS input determines whether the TMS34010 will be halted or begin executing instructions. The TMS34010 may be in one of two modes, host-present or self-bootstrap mode.

#### 1. Host-Present Mode

If HCS is high at the end of reset, TMS34010 instruction execution is halted and remains halted until the host clears the HLT (halt) bit in HSTCTL (host control register). Following reset, the eight RAS-only refresh cycles required to initialize the dynamic RAMs are performed automatically by the TMS34010 memory control logic. As soon as the eight RAS-only cycles are completed, the host is allowed access to TMS34010 memory. At this time, the TMS34010 begins to automatically perform DRAM refresh cycles at regular intervals. The TMS34010 remains halted until the host clears the HLT bit. Only then does the GSP fetch the level-0 vector address from location OFFFFFFE0h and begin executing its reset service routine.

#### 2. Self-Bootstrap Mode

If HCS is low at the end of reset, the TMS34010 first performs the eight RAS-only refresh cycles required to initialize the DRAMs. Immediately following the eight RAS-only cycles, the TMS34010 fetches the level-0 vector address from location OFFFFFEOh, and begins executing its reset service routine.

Unlike other interrupts and software traps, reset does not save previous ST or PC values. This is because the value of the stack pointer just before a reset is generally not valid, and saving its value on the stack is unnecessary. A TRAP 0 instruction, which uses the same vector address as reset, similarly does not save the ST or PC values.

#### asserting reset

A reset is initiated by asserting the RESET input pin at its active-low level. To reset the TMS34010 at power up. RESET must remain active low for a minimum of 40 local clock periods after power levels have become stable. At times other than power up, the TMS34010 is also reset by holding RESET low for a minimum of 40 clock periods. The 40-clock interval is required to bring TMS34010 internal circuitry to a known initial state. While RESET remains asserted, the output and bidirectional signals are driven to a known state.

The TMS34010 drives its  $\overline{\text{RAS}}$  signal inactive high as long as  $\overline{\text{RESET}}$  remains low. The specifications for certain DRAM and VRAM devices, including the TMS4161, TMS4164 and TMS4464 devices, require that the  $\overline{\text{RAS}}$  signal be driven inactive-high for 100 microseconds during system reset. Holding  $\overline{\text{RESET}}$  low for 150 microseconds will cause the  $\overline{\text{RAS}}$  signal to remain high for the 100 microseconds required to bring the memory devices to their initial states. DRAMs such as the TMS4256 specify an initial  $\overline{\text{RAS}}$  high time of 200 microseconds, requiring that  $\overline{\text{RESET}}$  be held low for 250 microseconds. In general, holding  $\overline{\text{RESET}}$  low for t microseconds ensures that  $\overline{\text{RAS}}$  remains high initially for t – 50 microseconds.

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# suspension of DRAM-refresh cycles during reset

An active-low level at the RESET pin is considered to be a power-up condition, and DRAM refresh is not performed until RESET goes inactive high. Consequently, the previous contents of the local memory may not be valid after a reset.

#### initial state following reset

While the RESET pin is asserted low, the TMS34010's output and bidirectional pins are forced to the states listed below.

OUTPUTS DRIVEN TO HIGH LEVEL	OUTPUTS DRIVEN TO LOW LEVEL	BIDIRECTIONAL PINS DRIVEN TO HIGH IMPEDANCE
DDOUT	BLANK	HSYNC
HRDY		VSYNC
DEN		HD0-HD15
t <del>A</del> L		LADO-LAD15
TR/QE		
RAS		
CAS		<u> </u>
₩		1
HINT		
HLDA/EMUA		

INITIAL STATE OF PINS FOLLOWING A RESET

Immediately following reset, all I/O registers are cleared (set to 0h), with the possible exception of the HLT bit in the HSTCTL register. The HLT bit is set to 1 if HCS is high just prior to the low-to-high transition of RESET.

Just prior to execution of the first instruction in the reset routine, the TMS34010's internal registers are in the following state:

- General-purpose register files A and B are uninitialized.
- The ST is set to 00000010h.
- The PC contains the 32-bit vector fetched from memory address OFFFFFEOh.

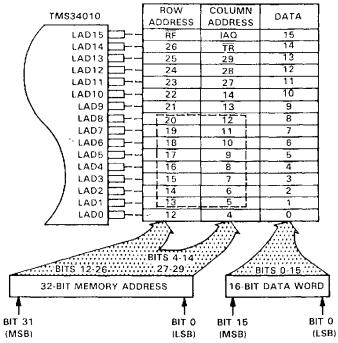
## TMS34010 local memory interface

The TMS34010 local memory interface consists of a triple-multiplexed address/data bus on which row addresses, column addresses, and data are transmitted. The associated memory control signals support direct interfacing to both DRAMs and VRAMs. At the beginning of a typical memory cycle, the address is output in multiplexed fashion as a row address followed by a column address. The remainder of the cycle is used to transfer data between the TMS34010 and memory.



# TMS34010 local memory interface

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RF : DRAM-REFRESH BUS STATUS BIT

1AQ - INSTRUCTION ACQUISITION BUS STATUS BIT

TR × VRAM SHIFT-REGISTER-TRANSFER BUS STATUS BIT

FIGURE 7. TRIPLE MULTIPLEXING OF ADDRESSES AND DATA

The following types of memory cycles are supported: read, write, VRAM memory-to-register, VRAM register-to-memory, RAS-only DRAM refresh and CAS-before-RAS DRAM refresh. The functional timing for these cycles is shown in the next six figures. Each memory cycle is a minimum of two maching states (a state is one local clock period) in duration. The seventh figure indicates the timing signals output during an internal cycle, i.e., a cycle during which no memory access takes place. An internal cycle is one state in duration.

During a memory cycle, the row address, column address, and data are transmitted over the same physical bus lines. The manner in which logical addresses are output at the memory interface makes external multiplexing hardware unnecessary, while supporting a wide variety of memory configurations. For example, in Figure 7, 16 consecutive address bits (5 through 20) are output on LAD1-LAD8 during the row and column address times. Output along with the address are bus status signals that indicate when DRAM refresh cycles, screen refresh (VRAM memory-to-register) cycles, and instruction fetch cycles are occurring.

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The following remarks apply to memory timing in general. A row address is output on LAD0-LAD15 at the start of the cycle, and is valid before and after the fall of RAS. Next a column address is output on LAD0-LAD15. The column address is valid briefly before and after the falling edge of LAL, but is not valid at the falling edge of CAS. The column address is clocked into an external transparent latch to g., a 74AS373 octal latch) on the falling edge of LAL to provide the hold time on the column address required for dynamic RAMs and video RAMs. A transparent latch is required in order that the row address be available at the outputs of the latch during the start of the cycle.

Very large memory configurations may require external buffering of data lines. The  $\overline{\text{DEN}}$  signal serves as the drive-enable signal to external bidirectional buffers, e.g., 74AS245 octal buffers. The DDOUT signal serves as the direction control for the buffers.

When an I/O register is addressed by the TMS34010, a special memory read or write cycle is performed. During this cycle, the external RAS signal falls, but the external CAS remains inactive-high for the duration of the cycle.

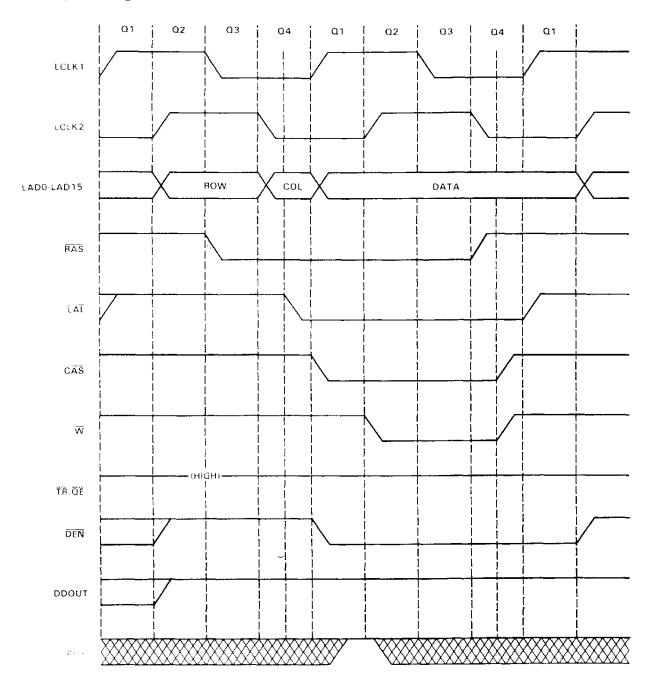
The timing shown in the first six functional timing diagrams assumes that the LRDY input remains high during the cycle. The LRDY pin is pulled low by slower memories requiring a longer cycle time. The TMS34010 samples the LRDY input at the end of Q1, as indicated in the figures. If LRDY is low, the LMS34010 inserts an additional state, called a "wait" state, into the cycle. Wait states continue to be inserted until LRDY is sampled at a high level. The cycle then completes in the manner indicated in the functional timing diagrams. A wait state is one local clock period in duration. Three additional timing diagrams provide examples of cycles extended by wait states.

The LRDY input is ignored by the TMS34010 during internal cycles.

A hold/hold acknowledge capability is also built into the local memory interface to allow external devices to request control of the bus. After acknowledging a hold request, the TMS34010 releases the bus by driving its address data bus and control outputs into high impedance.

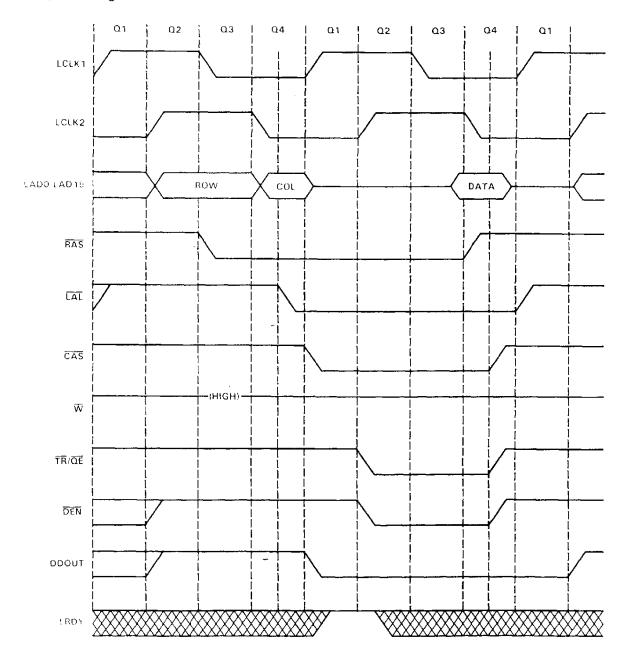
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# write cycle timing

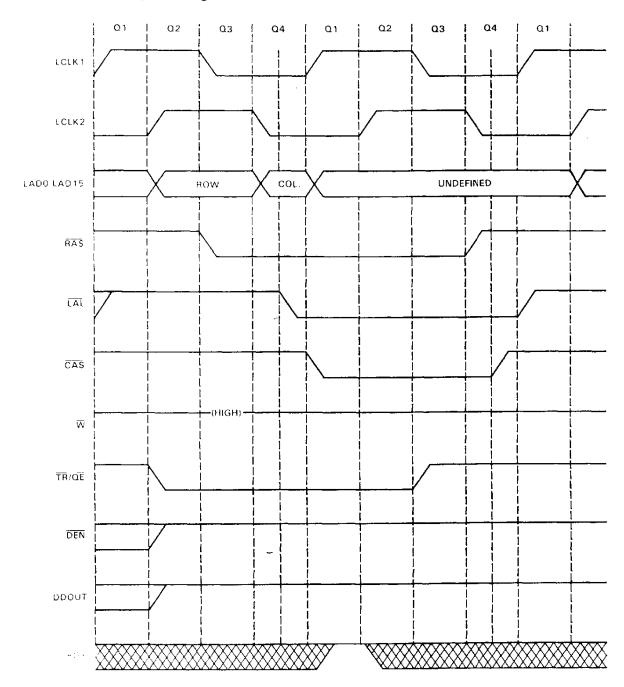


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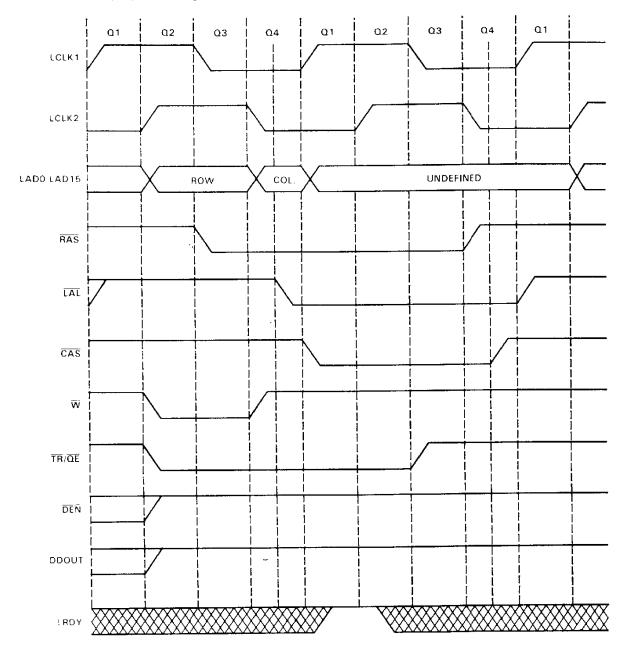
# read cycle timing



# memory-to-register cycle timing

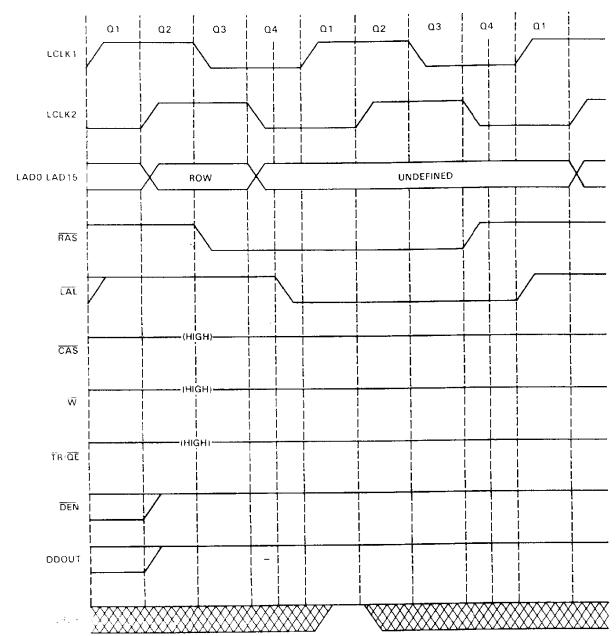


# register-to-memory cycle timing



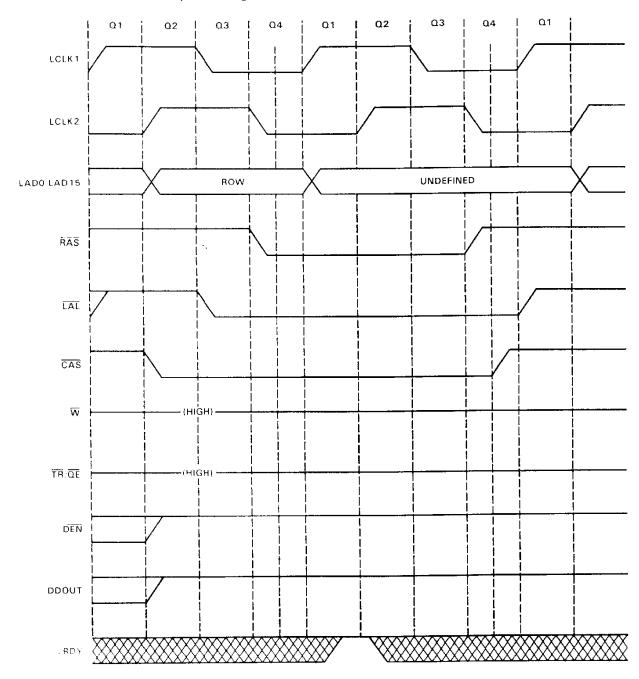
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# RAS-only DRAM refresh cycle timing



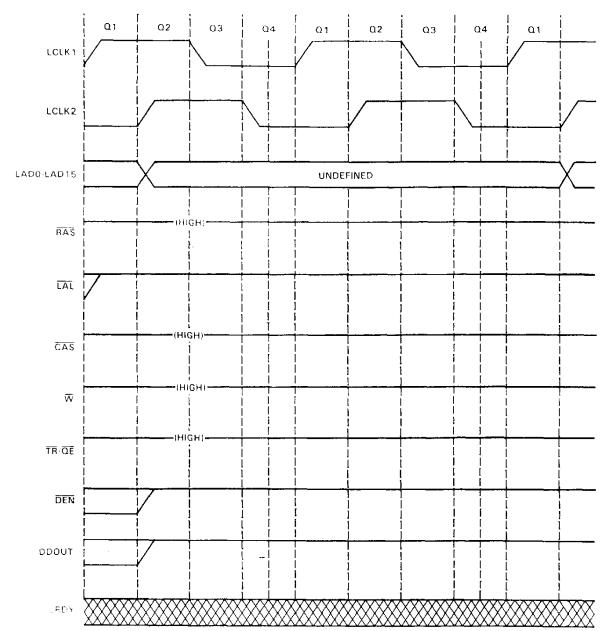
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# $\overline{\text{CAS}}\text{-before-RAS}$ refresh cycle timing



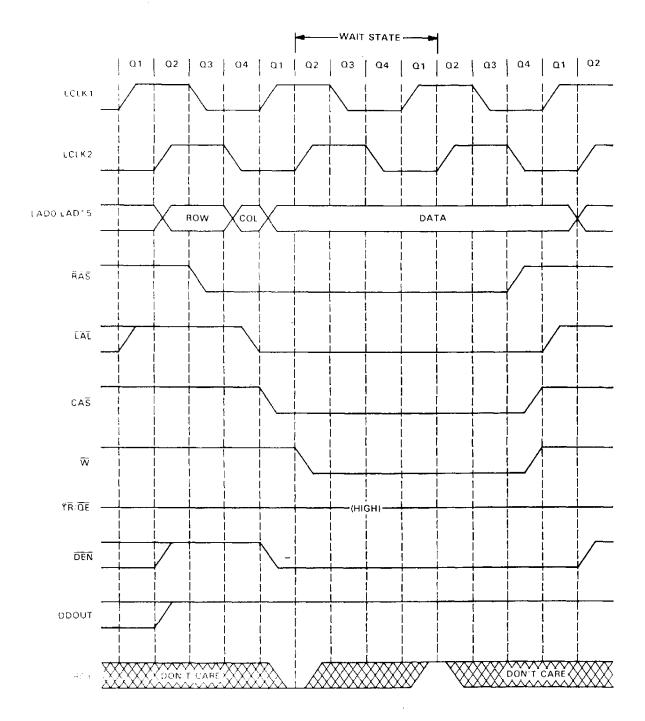
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# internal cycles back to back



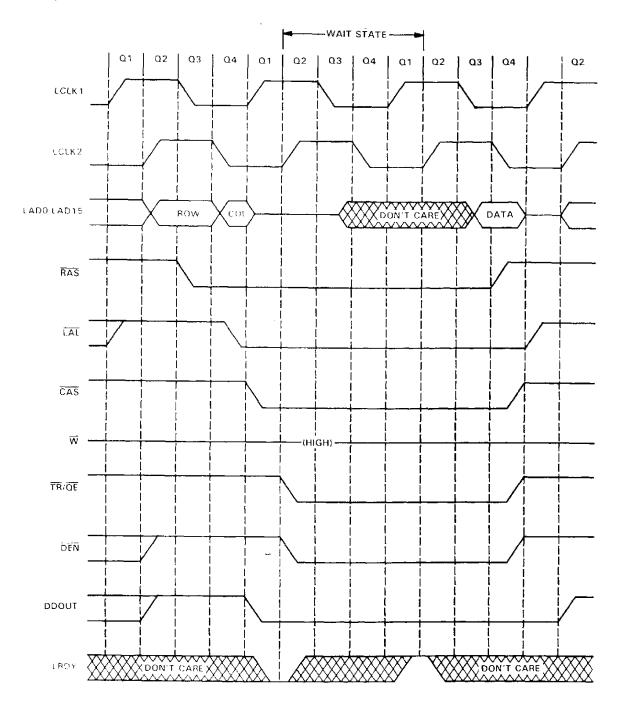
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write cycle with one wait state



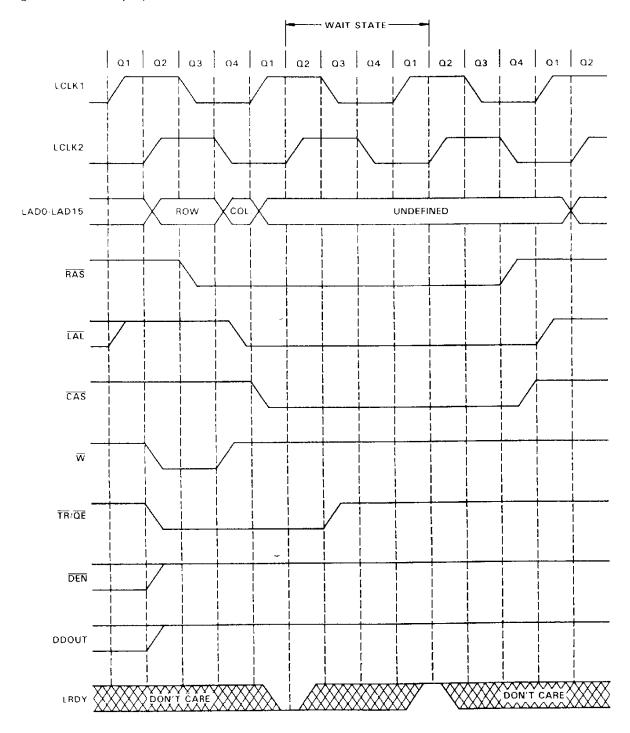


read cycle with one wait state



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register-to-memory cycle with one wait state



# **GRAPHICS SYSTEM PROCESSOR**

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# absolute maximum ratings over operating free-air temperature range<sup>1</sup>

Supply voltage, VCC	7 V
Input voltage range	.3 V to 20 V
Off-state output voltage range	-2 V to 7 V
Operating free-air temperature range	0°C to 70°C
Storage temperature range	°C to 150°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating 1.3 Fig. 1.1 and operation of the device at these or any other conditions beyond those indicated in the "Recommended Operating Conditions" the offices specify about the impred. Exposure to absolute maximum rated conditions for extended periods may affect device reliability contage values are with respect to the VSS pins of the chip.

## recommended operating conditions

		MIN	NOM	MAX	UNIT
Vcc	Supply voltage	4.75	5.0	5,25	V
VSS	Supply voltage <sup>†</sup>	0	0	0	V
Іон	High-level output current			- 400	μА
lOr.	Low-level output current			2.0‡	mA
T <sub>A</sub>	Operating free-air temperature			70	°C

Care should be taken by card designers to provide a minimum inductance path between the VSS pins and system ground in order to minimize VSS noise.

#### DC electrical characteristics

	PAR	AMETER	TEST CON	IDITIONS	MIN <sup>†</sup>	TYP <sup>‡</sup>	MAX <sup>†</sup>	UNIT	
V.)+§	High level input voltage, TTL-level	All inputs except INCLK	V <sub>CC</sub> = 5.0 V		2.2	v	CC+0.3	v	
	signal	INCLK	•00	5.0	3.0	_ v	CC+0.3		
VIL	Low level input voltage, TTL-evel	All inputs except INCLK			-0.3		0.8		
	signal	INCLK			-0.3		0.8		
۷ОН	High-level output voltage,  H TTL-level signa:		V <sub>CC</sub> = min,		2.6			V	
۷OL	Low-level output v	voltage,	VCC = max.		0.6			V	
10	High impedance leakage current, bidirectional pins		V <sub>CC</sub> = max	V <sub>O</sub> = 2.8 V V <sub>O</sub> = 0.6 V			20 - 20	μΑ	
ij	Input current	All inputs except RUN/EMU§	V <sub>I</sub> =V <sub>SS</sub>	to VCC			± 20	μΑ	
			V <sub>CC</sub> = ma	ax, 40 MHz			125	1	
ICC	Supply current		VCC = ma	ex, 50 MHz			150	mA	
~-			V <sub>CC</sub> = max, 60 MHz				175	ļ.,	
$c_1$	Input capacitance					10		pF	
co	Output capacitano address;data lines	·				10		pF	

<sup>&</sup>quot;For conditions shown as "min" or "max," use the appropriate value specified under "Recommended Operating Conditions.

<sup>&</sup>lt;sup>5</sup>RUN EMU will be no connected in a typical configuration. The nominal pull-up current will be 250 μA.



Dutput current of 2.0 mA is sufficient to drive five low-power Schottky TTL loads or 10 advanced low-power Schottky TTL loads (worst case).

As typical values are at  $V_{CC}=5$  V,  $T_A=25$  °C.

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signal transition levels



FIGURE 8. TTL-LEVEL OUTPUTS

TTL-level outputs are driven to a minimum logic-high level of 2.6 volts and to a maximum logic-low level of 0.6 volts. Output transition times are specified as follows.

For a high-to-low transition on a TTL-compatible output signal, the level at which the output is said to be "no longer high" is 2.0 volts, and the level at which the output is said to be "low" is 0.8 volts. For a low-to-high transition, the level at which the output is said to be "no longer low" is 0.8 volts, and the level at which the output is said to be "high" is 2.0 volts.

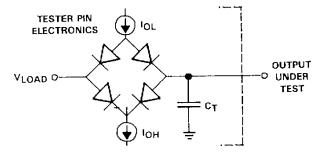


FIGURE 9. TTL-LEVEL INPUTS

Transition times for TTL-compatible inputs are specified as follows. For a high-to-low transition on an input signal, the level at which the input is said to be "no longer high" is 2.2 volts, and the level at which the input is said to be "low" is 0.8 volts. For a low to-high transition on an input signal, the level at which the input is said to be "no longer low" is 0.8 volts, and the level at which the input is said to be "high" is 2.2 volts.

### test measurement

The test load circuit shown in Figure 10 represents the programmable load of the tester pin electronics, which are used to verify timing parameters of TMS34010 output signals.



Where:  $l_{OL} = 2.0 \text{ mA DC}$  level verification (all outputs)

 $I_{OH} = 400 \, \mu A \, (all \, outputs)$ 

 $V_{LOAD} = 1.5 V DC$  level verification

0.7 V Timing verification

CT = 65 pF typical load circuit capacitance

FIGURE 10. TEST LOAD CIRCUIT

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## timing parameter symbology

Timing parameter symbols have been created in accordance with JEDEC Standard 100. In order to shorten the symbols, some of the pin names and other related terminology have been abbreviated as follows:

ΑL	LAL	HS	HSYNC or VSYNC
С	CAS	ICK	INCLK
CA	Column address	LR	LRDY
CK	LCLK1 and LCLK2	QE	TR/QE, when used as output enable
CK1	LCLK1	R	RAS
CK2	LCLK2	RA	Row address
CS	HCS	RS	HREAD
D	Data	RY	HRDY
DD	DDOUT	S	HREAD or HWRITE
EN	DEN	TR	TR/QE, when used as shift register enable
F	HFSO, HFS1	VCK	VCLK
HK	HLDA/EMUA	W	₩
HR	HOLD	WS	HWRITE

Lowercase subscripts and their meaning are:

- a access time
- c cycle time (period)
- d delay time
- h hold time
- su setup time
- t transition time
- t transmon time
- w pulse duration (width)

The following additional letters and symbols and their meaning are:

- H High
- L Low
- V Valid
- Z High impedance
- 1 No longer low
- No longer high

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## host interface timing parameters

The timing parameters for host interface signals are shown in the next four figures. The purpose of these figures and the accompanying table is to quantify the timing relationships among the various signals. The explanation of the logical relationships among signals will be found in the *TMS34010 User's Guide* (number SPVU001B).

The write strobe referred to in the following table is the enabling signal during a write to one of the host interface registers (see comment 2 on the next page). Similarly, the read strobe is the enabling signal during a read.

Quarter clock time  $t_Q$ , which appears in the following table, is one quarter of a local output clock period, or twice the input clock period,  $t_{CI(CK)}$ .

NO.	PARAMETER		TMS34010-40		TMS34010-50 TMS34010-60		UNIT
			MIN	MAX	MIN	MAX	
1	t <sub>SU</sub> (FV-SL)	Setup time of HWRITE/HREAD high or HFSO, HFS1 valid to read or write strobel	10		10		ns
2	†d(WSL-DV)	Delay from write strobe! to data in valid, write cycle		2tQ		2t <sub>Q</sub>	ns
3	<sup>t</sup> d(SL-SL)	Delay from read or write strobe low to next read or write strobe!	7tQ+10	-	7t <sub>Q</sub> + 10		ns
4	tw(SL)	Duration of read or write strobe low	во		80		ns
5	¹d(\$1+ \$L)	Delay from read or write strobe high to next read or write strobel	60		60		ns
6	GWSH DVI	Hold time of data in valid after write strobe high, write cycle	2		2		ns
7	IniSH FVI	Hold time of HWR(TE/HREAD high or HFSO, HFS1 valid after read or write strobe high	10		10		ns
8	th(RSL-DZ)	Hold time of data high impedance after read strobel, read cycle	O §		0 §		ns
9	td(RSL DV)	Delay from read strobe low to data out valid, read cycle with no wait		90		90	ns
10	tn(RSH-DV)	Hold time of data out valid after read strobel, read cycle	0		0		пѕ
11	lo(RSH DZ)	Delay from read strobe high to data out high impedance, read cycle		30 9		30 <sup>§</sup>	กร
12	thiCSL-RYHI	Hold time of HRDY high after HCS1, cycle with wait	0		0		ns
.3	d(CSL RYL)	Delay from HCS low to HRDY low, cycle with wait		40		40	ns
14	* WIRYLI	Pulse duration of HRDY low, cycle with wait		Ť		†	ns
1.5	la:RYL RYH;	Delay from HRDY) to HRDY high, cycle with wait	0‡		O‡		ns
. 6	<sup>т</sup> h,RYH-WSL	Hold time of write strobe low after HRDY*,	40	_	40		ns
17	to(RYH DV)	Delay from HRDY1 to data out valid, read cycle with wait		30		30	ns
18	th(RYH-RSL)	Hold time of read strobe low after HRDY1, read cycle with wait	40		40		ns

<sup>\*</sup>Parameter 14 is a function of local bus memory contention. This parameter is not tested. Refer to the TMS34010 User's Guide for details.

<sup>\*</sup>Parameter 15 is specified as minimum 0 ns to indicate that a low-going pulse on HRDY can be arbitrarily narrow.

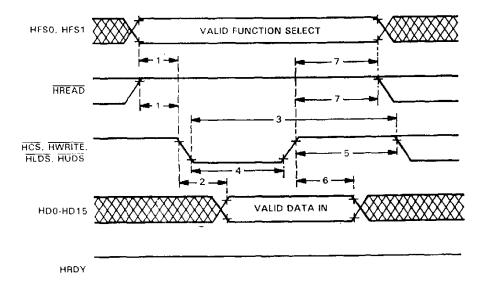
 $<sup>\</sup>S$ These values are derived from characterization and are not tested.

## general comments on host interface timing

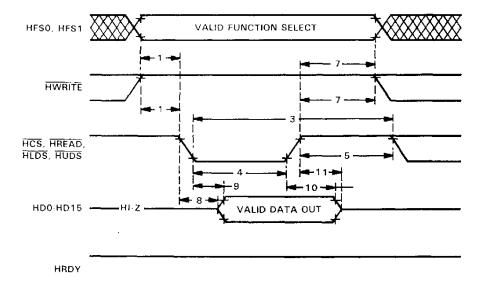
The following general comments apply to host interface timing:

- 1 The HRDY signal is enabled by an active low level on the HCS input. When HCS is inactive-high, HRDY is forced high regardless of the internal state of the device. Low-going transient pulses on HCS may result in low-going transient pulses on HRDY, but otherwise have no effect unless accompanied by active levels on other control signals.
- 2. A host interface write cycle occurs when HCS, HWRITE, and HLDS are low, or when HCS, HWRITE, and HUDS are low. The combination of these signals defines a write strobe. In either case, the last of the three signals to make the high-to-low transition is the strobe (write strobe) that begins the cycle. The first of the three signals to make the low-to-high transition ends the cycle. Similarly, a host interface read cycle occurs when HCS, HREAD, and HLDS are low, or when HCS, HREAD, and HUDS are low. The combination at these signals define a read strobe. In either case, the last of the three signals to make the high-to-low transition is the strobe (read strobe) that begins the cycle. The first of the three signals to make the low-to-high transition ends the cycle. All access times are specified with respect to the strobing edges that begin and end the cycle.
- 3. During a host interface read or write, HWRITE and HREAD must not be active-low simultaneously.
- 4. Host interface input signals HCS, HUDS, HLDS, HFSO, HFS1, HREAD, and HWRITE are assumed to be asynchronous with respect to the output clocks LCLK1 and LCLK2.

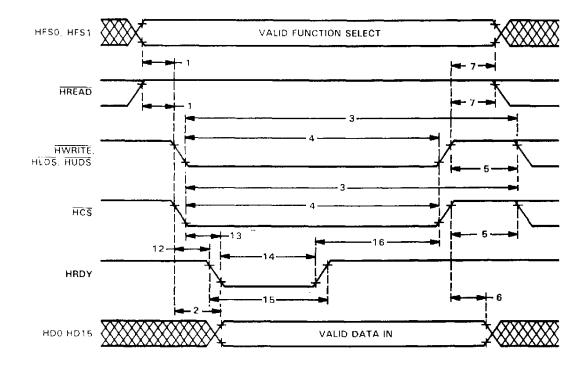
## host interface timing: write cycle with no wait



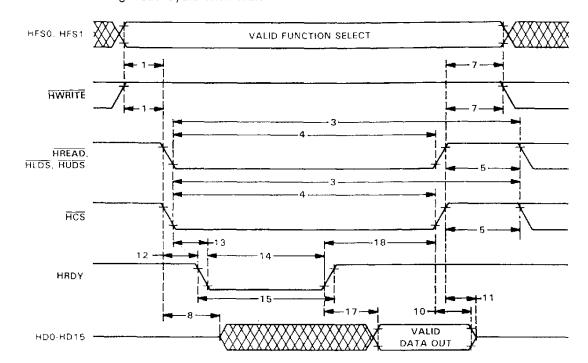
host interface timing: read cycle with no wait



host interface timing: write cycle with wait



host interface timing: read cycle with wait



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#### reset timing

The timing parameters for device reset are shown in the next two figures. The purpose of these figures is to quantify the timing relationships among the RESET, HCS, and LCLK1 signals. RESET and HCS are asynchronous inputs that are internally synchronized by latches internal to the TMS34010. The timing relationships specified for these signals relative to LCLK1 need be met only to guarantee recognition of a transition of one of these signals at a particular clock edge. The explanation of the logical relationships among signals will be found in the TMS34010 User's Guide.

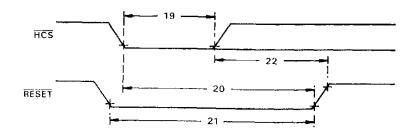
Quarter clock time  $t_Q$  which appears in the following table, is one quarter of a local output clock period, or twice the input clock period,  $t_C(ICK)$ .

NO.	PARAMETER		TMS34010-40		TMS34010-50 TMS34010-60		UNIT
				MAX	MIN	MAX	
19	tw(CSL)	Duration of HC\$ low to configure GSP to run in self-bootstrap mode	4ta+55		4t <sub>Q</sub> +55		กร
20	(su(CSL REH)	Setup time of HCS low to RESET1 to configure the GSP to run in self-bootstrap mode	8t <sub>Q</sub> + 55		8t <sub>Q</sub> + 55		ns
21	twiREL:	Duration of RESET low to ensure that GSP is properly reset	160t <sub>Q</sub> - 40		160t <sub>Q</sub> - 40		ns
22	td(CSH-REH)	Delay from HCS1 to RESET high, end of reset, to configure GSP to run in self-bootstrap mode		4t <sub>Q</sub> – 50 <sup>†</sup>		4ta - 50 <sup>†</sup>	ns
23	(su(REV-CK1L)	Setup time of RESET valid to LCLK11 to guarantee recognition at a particular clock edge	40‡		40‡		ns
24	th(CK1L-REV)	Hold time of RESET valid after LCLK1 low to guarantee recognition at a particular clock edge	10 <sup>‡</sup>		10 <sup>‡</sup>	-	ns
25	t <sub>su(CSV-CK1L)</sub>	Setup time of HCS valid to LCLK11 to guarantee recognition at a particular clock edge	40 <sup>‡</sup>		40 <sup>‡</sup>		ns
26	th(CK1L-CSV)	Hold time of HCS valid after LCLK1 low to guarantee recognition at a particular clock edge	10 <sup>‡</sup>		10‡		ns

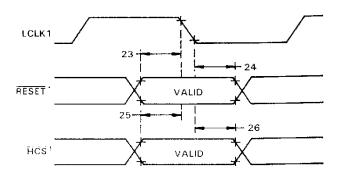
Parameter 22 is the maximum amount by which the RESET low-to-high transition can be delayed after the HCS low-to-high transition and still guarantee that the GSP is configured to run in self-bootstrap mode (HLT bit = 0) following the end of reset. HCS may be held to some time past the low-to-high RESET transition, and will be ignored by the GSP for 17 local clock periods following the clock edge at which the low-to-high RESET transition is detected. Following completion of the eight RAS-only cycles that automatically follow reset; however, a low HCS level will be interpreted as a chip select.

RESET and HCS are asynchronous inputs. The specified setup and hold times of these signals with respect to the high-to-low transition of LCLK1 need be met only to guarantee that a transition of RESET or HCS is detected by the device at a particular clock edge.

#### reset: asynchronous timing relationships



#### reset: synchronous timing relationships



TRESET and HCS are asynchronous inputs. The specified setup and hold times of RESET or HCS with respect to the high-to-low LCLK1 transition must be met only to guarantee that a RESET or HCS transition is detected by the device at a particular clock edge.

#### local bus timing parameters

The following six figures show the timing parameters for the signals of the local memory interface bus, often simply referred to as the local bus. The purpose of these figures and the accompanying tables is to quantify the timing relationships among the various signals. The explanation of the logical relationships among signals will be found in the *TMS34010 User's Guide* (number SPVU001B).

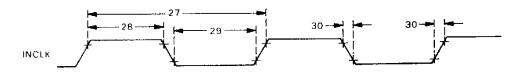
A number of parameter values are expressed in terms of quarter clock time tQ, which is one quarter of a local clock period, or twice the input clock period,  $t_{C(|CK|)}$ .

Input clock INCLK is divided internally by 8 to produce output clocks LCLK1 and LCLK2. Transitions of the other local interface output signals are also generated as delays from INCLK transitions. The dividedown logic that converts INCLK to the internal clocks used to generate LCLK1 and LCLK2 introduces significant propagation delays from the transitions of INCLK to the corresponding transitions of LCLK1 and LCLK2. While the frequency of INCLK is precisely eight times the frequency of LCLK1 or LCLK2, no timing relationship other than the frequency is specified between transitions of input clock INCLK and transitions of the output clocks LCLK1 and LCLK2.

			TMS34010-40		TMS34010-50		TMS34010-60		UNIT
NO		PARAMETER		MAX	MIN	MAX	MIN	MAX	UNIT
2.7	3c.ICK,	Penad of INCLK	25	62.5	20	62.5	16.5	62.5	ns
	WICKH,	Paise duration of INCLK high	81		8‡		6.5 <sup>‡</sup>		ns
29	LwilCKL)	Pulse duration of INCLK low	8:		8‡	· ·	6.5‡		ns
30	tulCK)	Transition time (rise and fall) of INCLK	2 †	8†	2†	8†	2†	8†	ns

These values are based on computer simulation and are not tested.

#### local bus timing: input clock



<sup>&</sup>lt;sup>‡</sup>This pulse width is tested at 1.4 volts.

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#### local bus timing parameters (continued)

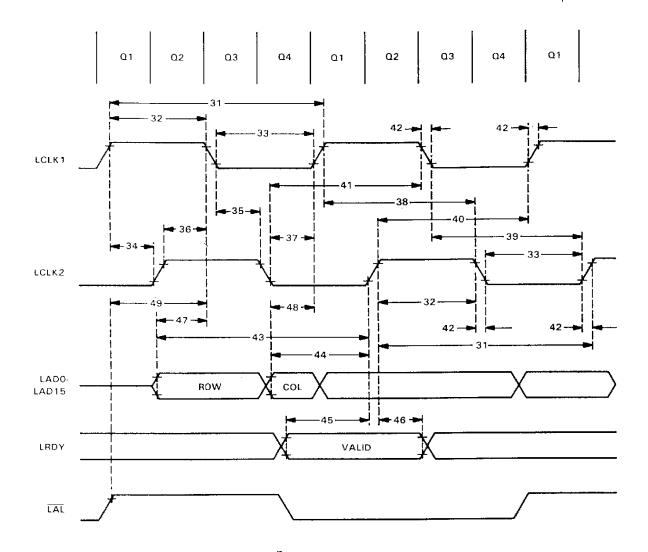
Quarter clock time  $t_{\mathbb{Q}}$ , which appears in the following table, is one quarter of a local output clock period. or 2tc(ICK).

NO.	PARAMETER	TMS34010-40		TMS34010-50 TMS34010-60		UNIT
		MIN	MAX	MIN	MAX	
31	t <sub>C(CK)</sub> Period of local clocks LCLK1 and LCLK2	8t <sub>c(ICK)</sub> †		8t <sub>c(ICK)</sub> †		ns
32	tw(CKH) Pulse duration of local clock high	2tQ - 10		2t <sub>Q</sub> - 10		กร
33	(w(CKL) Pulse duration of local clock low	2t <sub>Q</sub> - 10		2t <sub>Q</sub> - 10		ns
34	In(CK1H-CK2L) Hold time of LCLK2 low after LCLK1 high	t <sub>Q</sub> - 10		t <sub>Q</sub> - 10		ns
35	Fh(CK1L-CK2H) Hold time of LCLK2 high after LCLK1 low	t <sub>Q</sub> - 10		t <sub>Q</sub> - 10		ns
36	In(CK2H CK1H) Hold time of LCLK1 high after LCLK2 high	t <sub>Q</sub> ~ 10		t <sub>Q</sub> - 10		ns
3.7	ThiCK2L-CK1Li Hold time of LCLK1 low after LCLK2 low	ι <sub>Q</sub> 10		t <sub>Q</sub> - 10		ns
38	th(CK1H-CK2H) Hold time of ECLK2 high after LCLK1 high	31 <sub>Q</sub> - 10		3tQ 10		กร
39	th(CK1L CK2L) Hold time of LCLK2 low after LCLK1 low	3t <sub>0</sub> - 10		3tQ - 10		r:s
40	th(CK2H-CK1L) Hold time of LCLK1 low after LCLK2 high	3t <sub>0</sub> - 10		31 <sub>0</sub> - 10		ns
41	th(CK2L-CK1H) Hold time of LCLK1 high after LCLK2 low	3t <sub>Q</sub> - 10		3t <sub>Q</sub> - 10		ns
42	tt Transition time (rise and fall) of LCLK1 or LCLK2		10		10_	ns
43	t <sub>su(RAV-CK2H)</sub> Setup time of row address valid to LCLK21	4t <sub>Q</sub> ~ 25		4tQ - 15	· · · · ·	ns
44	t <sub>SU(CAV-CK2H)</sub> Setup time of column address valid to LCLK21	2t <sub>Q</sub> ~ 25		2t <sub>Q</sub> – 15		ns
45	t <sub>SU(LRV-CK2H)</sub> Setup time of LRDY valid to LCLK21	30 <sup>‡</sup>		30‡		กร
46	thiCK2H-LRVi Hold time of LRDY valid after LCLK2 high	0‡		0 !		ns
47	tsu(RAV-CK1L) Setup time of row address valid to LCLK11	t <sub>Q</sub> - 25		t <sub>Q</sub> – 15		ns
.18	t <sub>SUICAV-CK1H</sub> ) Setup time of column address valid to LCLK11	t <sub>Q</sub> - 25		t <sub>Q</sub> – 15		ns
49	tsurALH-CK1L) Setup time of LAL high to LCLK11	2t <sub>O</sub> - 20		2tQ 10		ns

This is a functional minimum and is not tested. This parameter can also be specified as 4tg. FLRDY is a synchronous input sampled during the low-to-high transition of LCLK2. The specified setup and hold times must be met for the device to operate properly.

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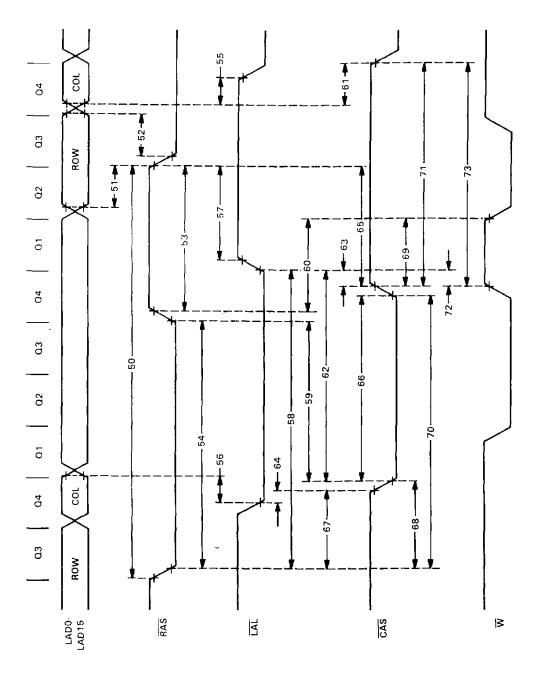
local bus timing: output clock and LRDY signal



NO.		PARAMETER	TMS34010-40 MIN MAX	TMS34010-50 MIN MAX	TMS34010-60 MIN MAX	UNIT
50	'd(RL-RL)	Delay from RASI to RASI	8tO †	8tQ1	BtQ <sup>†</sup>	ns
51	¹su(RAV-RL)	Setup time of row address valid to RASI	t <sub>Q</sub> - 20	t <sub>Q</sub> – 15	t <sub>Q</sub> - 15	ns
52	†h(RL-RAV)	Hold time of row address valid after RAS low	t <sub>Q</sub> - 20	t <sub>Q</sub> – 10	t <sub>Q</sub> – 5	ns
53	tw(BH)	Pulse duration, RAS high	$3t_{\Omega} - 20$	3t <sub>Q</sub> - 10	3t <sub>Q</sub> – 5	ns
54	tw(RL)	Pulse duration, RAS low	5t <sub>Q</sub> 20	5t <sub>Q</sub> – 10	5t <sub>Q</sub> – 10	ns
55	<sup>t</sup> su(CAV-ALL)	Setup time of column address valid to TAL1	0.5t <sub>Q</sub> -20	0.5t <sub>Q</sub> - 10	0.5t <sub>Q</sub> 10	. ns
56	<sup>t</sup> h(ALL-CAV)	Hold time of column address valid after LAL low	0.5t <sub>Q</sub> - 15	0.5tQ - 10	0.5t <sub>Q</sub> - 10	ns
57	th(ALH-RH)	Hold time of RAS high after LAL high	2tQ 20	2t <sub>Q</sub> - 10	2t <u>n</u> – 10	ns
58	ThtRL-ALLI	Hold time of LAL low after RAS low	6t <sub>Q</sub> – 20	6tQ - 10	6t <sub>0</sub> 10	ns
59	¹h(CtRL)	Hold time of RAS low after CAS low	3t <sub>Q</sub> – 20	3t <sub>Q</sub> – 10	3t <sub>Q</sub> – 10	ns
60	th(RH-WH)	Hold time of W high after after RAS high, shift register transfer follows read	2t <sub>Q</sub> · 20	2t <sub>Q</sub> – 10	2t <sub>Q</sub> ~ 10	ns
61	Isu(CAV-ĈL)	Setup time of column address valid to CAS:	t <sub>Q</sub> – 20	tQ 10	t <sub>Q</sub> – 10	ns
62	th(CL-ALL)	Hold time of LAL low after CAS low	4t <sub>Q</sub> - 20	41 <sub>Q</sub> - 10	41 <sub>Q</sub> - 10	ns
63	Th(CH ALL)	Hold time of LAL low after CAS high, write cycle	0.5t <sub>Q</sub> 15	0.5tQ - 10	0.5t <sub>Q</sub> - 10	ns
64	\h(ALL-CH)	Hold time of CAS high after LAL low	0.5t <sub>Q</sub> - 15	0.5tQ - 10	0.5t <sub>Q</sub> - 10	ns
65	th(CH RH)	Hold time of RAS high after CAS high	2.5tQ - 15	2.5tQ - 10	2.5t <sub>Q</sub> – 10	ns
66	tw(CL)	Pulse duration, CAS low	3.5t <sub>Q</sub> – 25	3.5t <sub>Q</sub> - 10	3.5t <sub>Q</sub> 10	ns
67	th(RL-CH)	Hold time of CAS high after RAS low	2t <sub>Q</sub> – 20	2t <sub>Q</sub> - 10	2tQ - 10	ns
68	<sup>t</sup> d(RL-CLI	Delay time from RAS low to CAS low	2tQ + 20	21 <sub>Q</sub> + 10	2t <sub>Q</sub> + 10	ns
69	<sup>t</sup> h(CH-WH)	Hold time of $\overline{W}$ high after $\overline{CAS}$ high, shift register transfer follows read	1.5t <sub>Q</sub> – 15	1.5t <sub>Q</sub> - 10	1.5t <sub>Q</sub> – 10	ns
70	<sup>լ</sup> ո(RL-CL)	Hold time of CAS low after RAS low	5.5t <sub>Q</sub> – 25	5.5t <sub>Q</sub> – 10	5.5ta - 10	ns
71	tw(CH)	Pulse duration, CAS high	4.5t <sub>Q</sub> – 15	4.5t <sub>Q</sub> - 10	4.5t <sub>Q</sub> – 10	ns
72	th(WH-ALL)	Hold time of LAL low after W high, write cycle	0.5t <sub>Q</sub> – 15	0.5t <sub>Q</sub> - 10	0.5t <sub>Q</sub> - 10	ns
73	¹su(WH-CL)	Setup time of $\overline{W}$ high to $\overline{CAS}\downarrow$ , end of write	4.5t <sub>Q</sub> – 15	4.5t <sub>Q</sub> – 10	4.5t <sub>Q</sub> - 10	ns

This is a functional minimum and is not tested.

local bus timing: the RAS, CAS, and LAL outputs



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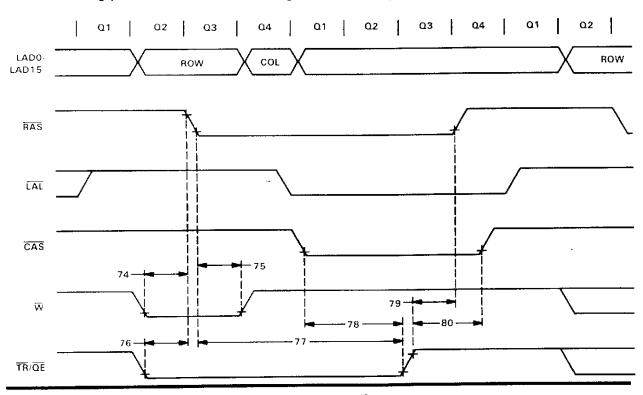
#### local bus timing parameters (continued)

Quarter clock time  $t_Q$ , which appears in the following table, is one quarter of a local output clock period, or  $2t_C(ICK)$ .

NO.	PARAMETER		TMS34010-40		TMS34010-50 TMS34010-60		UNIT
				MAX	MIN	MAX	
74	so(WL RL)	Setup time of $\widetilde{W}$ low to $\overline{RAS1}$ , serial register transfer cycle	t <sub>Q</sub> - 20		tQ 10	)	ns
75	th(RL-WL)	Hold time of W low after RAS low, serial register transfer cycle	t <sub>Q</sub> – 20		t <sub>Q</sub> 10	)	ns
76	su(TRL-RL)	Setup time of TR/QE low to RASI, serial register transfer cycle	t <sub>Q</sub> - 20		t <sub>Q</sub> – 10	)	ns
77	th(RL-TRL)	Hold time of TR/QE low after RAS low, serial register transfer cycle	41 <u>0</u> - 20		4t <sub>Q</sub> – 10	)	ns
78	th(CL-TRL)	Hold time of TR/QE low after CAS low, serial register transfer, cycle	2t <sub>Q</sub> - 20		2t <sub>Q</sub> - 10	)	ns
79	t <sub>su</sub> (TRH-RH)	Setup time of TR/QE high to RAS1, serial register transfer cycle	tQ 20		t <sub>Q</sub> - 10	)	ns
80	<sup>t</sup> su(TRH-CH)	Setup time of TR/QE high to CAS1, serial register transfer cycle	1.5t <sub>Q</sub> - 25		1.5t <sub>Q</sub> - 10	)	ns

NOTE: Parameters §1 and 82 intentionally omitted.

#### local bus timing parameters: VRAM serial register transfer cycle



## local bus timing parameters (continued)

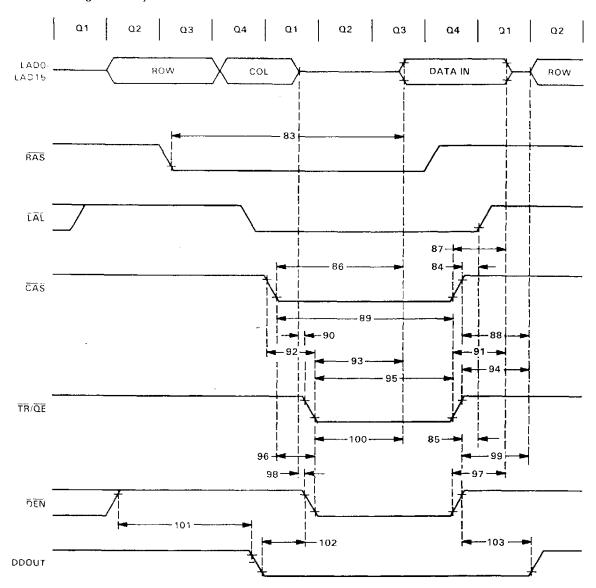
Quarter clock time tQ, which appears in the following table, is one quarter of a local output clock period, or 2tc(ICK).

NO.	PARAMETER		TMS34	010-40	TMS34		UNIT
			MIN	MAX	MIN	MAX	
83	<sup>t</sup> a(RL-DV)	Access time from RAS low to data in valid, read cycle		5.5tQ - 40 <sup>†</sup>		5.5tQ - 25 <sup>†</sup>	ns
84	t <sub>su</sub> (CH-ALH)	Setup time of CAS high to LAL!	0.5t <sub>Q</sub> - 15		0.5t <sub>Q</sub> 10		ns
85	t <sub>su</sub> (ENH-ALH)	Setup time of OEN high to LALT	0.5t <sub>O</sub> - 15		0.5t <sub>Q</sub> - 10		ns
56	ta(CL-DV)	Access time from CAS low to data in valid, read cycle		3.5t <sub>Q</sub> - 40 <sup>†</sup>		3.5t <sub>Q</sub> - 25 <sup>‡</sup>	ns
87	<sup>ኒ</sup> ክ(CH-DV)	Hold time of data in valid after CAST, read cycle	0		. 0		ns
88	th(CH-RAZ)	Hold time of row address high impedance after $\overline{\text{CAS}}$ high, end of read cycle	1.5t <sub>Q</sub> - 10 <sup>‡</sup>		1.5t <sub>Q</sub> 10‡		ns
89	th(CL-QEL)	Hold time of TR/QE low after CAS low, read cycle	3.5t <sub>Q</sub> - 25		3.5t <sub>Q</sub> - 10		пs
90	t <sub>su(CAZ-QEL)</sub>	Setup time of column address high impedance to TR/QE1, read cycle	t <sub>Q</sub> - 10‡		t <sub>Q</sub> - 10 <sup>‡</sup>		ns
91	th(QEH-DV)	Hold time of data in valid after $\overline{TR}/\overline{QE}t$ , read cycle	0		0		ns
92	td(CL-QEL)	Delay time from CAS4 to TR/QE low, read cycle		t <sub>Q</sub> + 20		t <sub>Q</sub> + 10	ns
93	ta(QEL-DV)	Access time from TR/QE low to data in valid, read cycle		2.5t <sub>Q</sub> - 40 <sup>†</sup>		2.5t <u>o</u> 25 <sup>†</sup>	ns
94	th(QEH-RAZ)	Hold time of row address high impedance after TR/QE high, end of read cycle	1.5tg 10 <sup>‡</sup>		1.5t <sub>Q</sub> - 10 <sup>‡</sup>		ns
95	tw(OEL)	Pulse duration, TR/QE low, read cycle	2.5t <sub>Q</sub> 25	·	2.5t <sub>Q</sub> - 10		ns
96	ta(CL-ENL)	Delay time from CAS low to DEN low, read cycle	1	t <sub>Q</sub> + 20		t <sub>Q</sub> + 10	ns
97	th(ENH-DV)	Hold time of data in valid after DENI, read cycle	0		0		ns
98	tsu(CAZ-ENL)	Setup time of column address high impedance to DENI, read cycle	t <sub>Q</sub> - 10 <sup>‡</sup>		t <sub>Q</sub> 10‡		ns
99	<sup>t</sup> h(ENH-RAZ)	Hold time of next row address high impedance after $\overline{\text{DEN}}$ high, end of read cycle	1.5tQ · 10‡		1.5t <sub>Q</sub> - 10 <sup>‡</sup>		ns
100	¹a(ENL-DV)	Access time from DEN low to data in valid, read cycle		2.5tQ 40 <sup>†</sup>		2 5tQ 25 <sup>†</sup>	ns
101	In(ENH-DDH)	Hold time of DDOUT high after DEN high, read follows write cycle	3t <sub>Q</sub> - 20		3t <sub>Q</sub> - 10		ns
102	tsu(DDL-ENL)	Setup time of DDOUT low to DEN1, read cycle	t <sub>Q</sub> - 20		t <sub>Q</sub> – 10		ns

 $<sup>^{\</sup>dagger}4_{TQ}$  is added to these values for each wait state inserted.  $^{\dagger}$  These values are derived from characterization and are not tested.

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## local bus timing: read cycle



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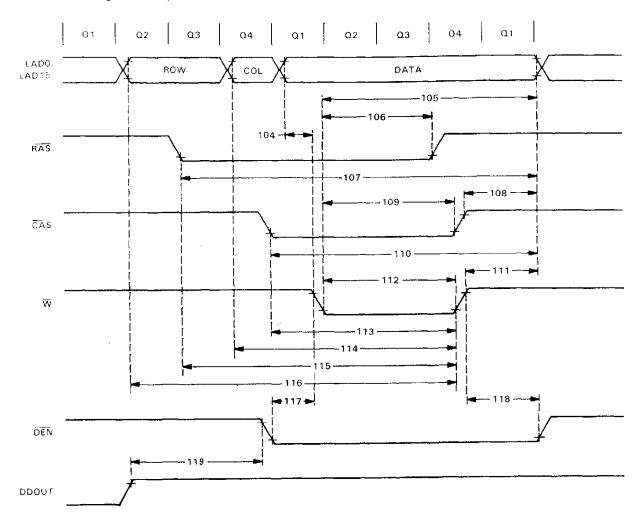
## local bus timing parameters (continued)

Quarter clock time  $t_Q$ , which appears in the following table, is one quarter of a local output clock period, or  $2t_C(ICK)$ .

NO.	PARAMETER		TMS340	10-40	TMS340		UNIT
	ļ		MIN	MAX	MIN	MAX	Ī
103	th(ENH-DDL)	Hold time of DDOUT low after DEN high, read cycle	1.5t <sub>Q</sub> - 15		1.5t <sub>Q</sub> - 10		ns
104	Tsu(DV-WL)	Setup time of data out valid to W1, write cycle	ta - 20		t <sub>Q</sub> – 15		ns
105	thtWE-DVI	Hold time of data out valid after $\overline{\mathbf{W}}$ low, write cycle	4t <sub>O</sub> - 20		4t <sub>Q</sub> - 10		ns
106	Is_(WL-RH)	Sctup time of W low to RASI, write cycle	2t <sub>Q</sub> - 20		2t <sub>Q</sub> - 10		ns
107	<sup>t</sup> h(RL-DV)	Hold time of data out valid after RAS low, write cycle	7t <sub>Q</sub> – 20		7t <sub>Q</sub> - 10		ns
108	¹h(CH-DV)	Hold time of data out valid after CAS high, write cycle	1.5t <sub>Q</sub> - 15		1.5tQ - 10		ns
109	¹su(WL-CH)	Setup time of W low to CAS1, write cycle	2.5t <sub>Q</sub> - 25		2.5t <sub>Q</sub> - 10		ns
110	th(CL-DV)	Hold time of data out valid after CAS low, write cycle	5t <sub>Q</sub> – 20		5tQ ~ 10		ns
111	th(WH-DV)	Hold time of data out valid after $\overline{W}$ high, write cycle	1.5t <sub>Q</sub> - 15		1.5t <sub>Q</sub> - 10		ns
112	TwiWLi	Pulse duration, W low	2.5t <sub>Q</sub> - 25		2.5t <sub>Q</sub> - 10		ns
113	INCL WUI	Hold time of $\overline{\mathbb{W}}$ low after $\overline{\mathbb{CAS}}$ low, write cycle	3.5t <sub>Q</sub> - 25		3.51 <sub>Q</sub> - 10		ns
114	(su(CAV-WH)	Setup time of column address valid to $\overline{W}^{\pm},$ write cycle	4.5t <sub>Q</sub> - 30		4.5t <sub>Q</sub> - 15		ns
115	th(RL-WL)	Hold time of $\overline{\mathbb{W}}$ low after $\overline{RAS}$ low, write cycle	5.5t <sub>Q</sub> - 25		5.5t <sub>Q</sub> - 10		ns
116	I <sub>SU(RAV-WH)</sub>	Setup time of row address valid to $\overline{W}^*$ , write cycle	6.5t <sub>Q</sub> - 35		6.5t <sub>Q</sub> - 15	_	ns
117	tsu(ENL-WL)	Setup time of DEN low to W1, write cycle	t <sub>Q</sub> - 20		t <sub>Q</sub> 10		ns
118	th(WH-ENL)	Hold time of $\overline{\text{DEN}}$ low after $\overline{W}$ high, write cycle	1.5t <sub>Q</sub> - 15		1.5t <sub>Q</sub> - 10		ns
119	<sup>t</sup> su(DDH-ENL)	Setup time of DDOUT high to DEN1, write follows read	3t <sub>Q</sub> - 20		3t <sub>Q</sub> – 10		ns

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local bus timing: write cycle



#### local bus timing parameters (continued)

Quarter clock time  $t_Q$ , which appears in the following table, is one quarter of a local output clock period, or  $2t_C(ICK)$ .

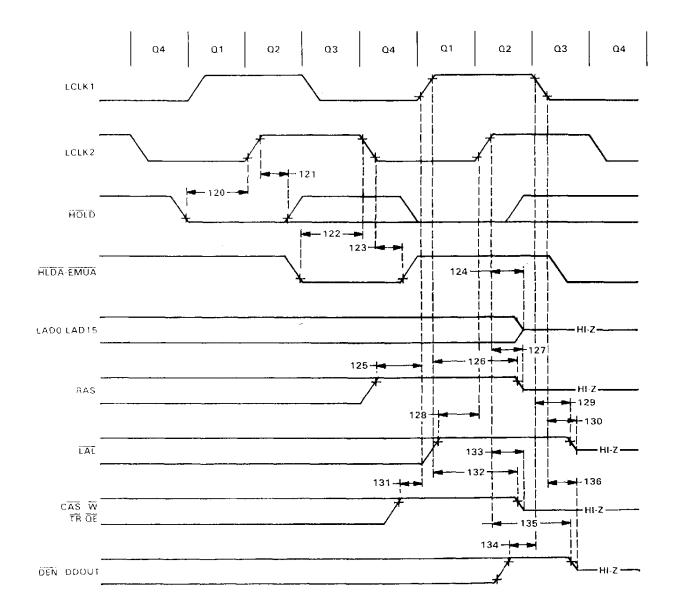
NO.		PARAMETER	TMS3401	10-40	TMS34010-50 TMS34010-60		UNIT
			MIN	MAX	MIN	MAX	
120	TsucHRV CK2H)	Setup time of HOLD valid to LCLK21	50 <sup>†</sup>		401		ns
121		Hold time of HOLD valid after LCLK2 high	of		01		ins
122	t <sub>su(HKV-CK2L)</sub>	Setup time of HLDA/EMUA output valid before LCLK21	1 <sub>Q</sub> - 20		t <sub>Q</sub> = 10		ns
123	¹n(CK2L-HKL)	Hold time of HLDA/EMUA low, after LCLK2 low	t <sub>Ω</sub> 15		t <sub>Q</sub> – 15		пѕ
124	<sup>t</sup> d(CK2H-DZ)	Delay from LCLK2 high to LAD pins high impedance, bus release		30 <sup>‡</sup>		30‡	ns
125	t <sub>su</sub> (RH-CK1H)	Setup time of RAS high to LCLK11	t <sub>Q</sub> - 20		t <sub>Q</sub> - 10		ns
126	¹h(CK1H RH)	Hold time of RAS driven high after LCLK1 high, bus release	t <sub>0</sub> - 10 <sup>‡</sup>		t <sub>Q</sub> - 10‡		ns
127	¹d(CK2H-RZ)	Delay from LCLK2 high to RAS high impedance, bus release		30‡		30‡	ns
128	tsu(ALH-CK2H)	Setup time of LAL high to LCLK21	tQ - 20		t <sub>O</sub> – 10		ns
129	thiCK1L-ALH)	Hold time of LAL driven high after LCLK11, bus release	- 5 <sup>‡</sup>		~5 <sup>‡</sup>		ns
130	<sup>t</sup> d(CK1L-ALZ)	Delay from LCLK1 low to LAL high impedance, bus release		30‡		304	n <b>5</b>
131	t <sub>su</sub> (CH-CK1H)	Setup time of CAS, W, and TR/QE high to LCLK11	0.5tQ - 15		0.5t <sub>Q</sub> – 10		ns
132	¹h(CK1H-CH)	Hold time of CAS, W, and TR/QE high after LCLK1 high, bus release	tQ-10 <sup>‡</sup>		t <sub>Q</sub> – 10 <sup>‡</sup>		ns
133	td(CK2H-CZ)	Delay from LCLK2 high to $\overline{CAS}$ , $\overline{W}$ , and $\overline{TR}/\overline{QE}$ high impedance, bus release		30 <sup>‡</sup>		30‡	ns
134	tsu(ENH-CK2H)	Setup time of DEN or DDOUT high to LCLK11	t <sub>Q</sub> - 20		t <sub>Q</sub> ~ 10		ns
135	th(CK2H-ENH)	Holo time of DEN and DDOUT high after LCLK11, bus release	tQ - 10 <sup>‡</sup>		t <sub>Q</sub> - 10 <sup>‡</sup>		ns
136	¹d(CK1L-ENZ)	Delay from LCLK1 low to DFN and DDOUT high impedance, bus release		30 <sup>‡</sup>		301	ns
137	<sup>t</sup> h(CK2H-DZ)	Hold time of LAD bus high impedance after LCLK21	-5 <sup>‡</sup>		-5 <sup>‡</sup>		ns
138	th(CK2H-RZ)	Hold time of RAS, CAS, W, LAL, and TR/QE high impedance after LCLK11	5 <sup>‡</sup>		- 5 <sup>‡</sup>		ns
139	<sup>‡</sup> d(CK1H-RH)	Delay from LCLK1 high to RAS, $\overline{CAS}$ , $\overline{W}$ , $\overline{LAL}$ , and $\overline{TR}/\overline{QE}$ driven high, resume bus control		30		30	ns
140	th(CK2H-RH)	Hold time of RAS high after LCLK2 high, resumes bus control	tQ-15		ta-10		ns
141	thiCK2H-CH)	Hold time of CAS, W. and TR/QE high after LCLK2 high, resume bus control	5‡		-5‡		пѕ

<sup>\*</sup>HOLD is a synchronous input sampled during the low to-high transition of LCLK2. The specified setup and hold times must be met for the device to operation properly.

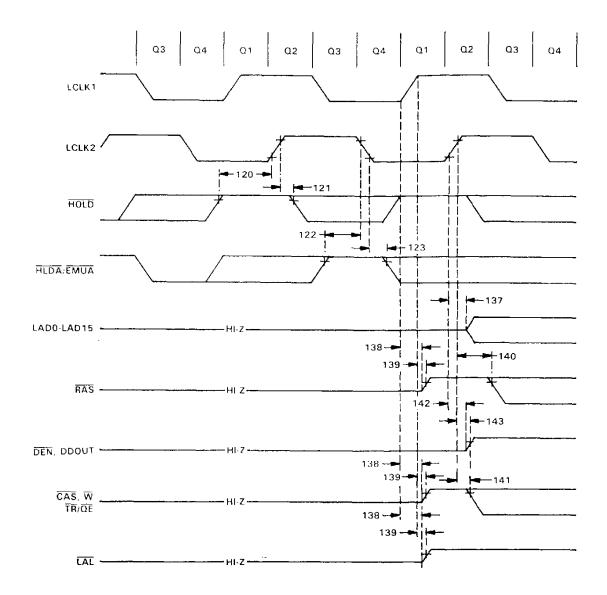
<sup>\*</sup>These values are derived from characterization and are not tested.

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GSP releases control of local bus



## GSP resumes control of local bus



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## local bus timing parameters (continued)

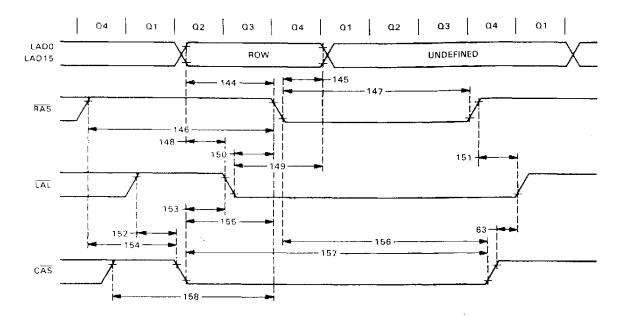
Quarter clock time  $t_Q$ , which appears in the following table, is one quarter of a local output clock cycle, or  $2t_C(ICK)$ .

NO.	PARAMETER		TMS340	10-40	TM\$34010-50 TM\$34010-60		UNIT
			MIN	MAX	MIN	MAX	
142	th(CK2H-ENZ)	Hold time of DEN, DDOUT high impedance after LCLK2 high, resume bus control	<b>-</b> 5 <sup>†</sup>		- 5 <sup>†</sup>		ns
143	¹d(CK2H-ENH)	Delay from LCLK2 high to DEN, and DDOUT driven high, resume bus control		30		30	ns
144	<sup>t</sup> su(RAV-RL)	Setup time of row address valid to RASI, CAS-before-RAS refresh	2t <sub>Q</sub> – 25		2t <sub>Q</sub> - 15		ns
145	<sup>t</sup> h(RL-RAV)	Hold time of row address valid after RAS low, CAS-before-RAS refresh	t <sub>Q</sub> – 20		t <sub>Q</sub> - 10		ns
146	tw(RH)	Pulse duration, RAS high, start of CAS-before-RAS refresh	4tQ - 20		4t <sub>Q</sub> - 10		ns
147	tw(RL)	Pulse duration, RAS low, CAS-before-RAS refresh	4t <sub>Q</sub> - 20		4t <sub>Q</sub> - 10		ns
148	tsu(RAV-ALL)	Setup time of row address valid to LALI,  CAS-before-RAS refresh	t <sub>Q</sub> - 20		t <sub>Q</sub> – 15		ns
149	th(ALL-RAV)	Hold time of row address valid after LAL low, CAS-before-RAS refresh	2t <sub>Q</sub> - 20		2t <sub>Q</sub> - 10		ns
150	<sup>‡</sup> h(ALL-RH)	Hold time of RAS high after EAL low.  CAS-before-RAS refresh	t <sub>Q</sub> - 20		t <sub>Q</sub> – 10		ns
151	<sup>t</sup> su(RH-ALH)	Setup time of RAS high to LAL1, CAS-before-RAS refresh	t <sub>Q</sub> – 20		t <sub>Q</sub> - 10		ns
152	<sup>T</sup> su(ALH-CL)	Setup time of LAL high to CAS:, CAS-before-RAS refresh	t <sub>Q</sub> – 20		t <sub>Q</sub> - 10		ns
153	<sup>t</sup> su(CL-ALL)	Setup time of CAS low to LALI, CAS-before-RAS refresh	tQ - 20	_	t <sub>Q</sub> – 10		ns
154	<sup>t</sup> su(RH-CL)	Setup time of RAS high to CASI, CAS-before-RAS refresh	2t <sub>Q</sub> - 20		2t <sub>Q</sub> - 10		ns
155	<sup>t</sup> su(CL-RL)	Setup time of CAS low to RAS1, CAS-before-RAS refresh	2t <sub>Q</sub> – 20		2t <sub>Q</sub> - 10		ns
156	<sup>t</sup> h(RL-CL)	Hold time of CAS low after RAS low, CAS-before-RAS refresh	4.5t <sub>Q</sub> - 25		4.5t <sub>Q</sub> - 10		ns
157	tw(CL)	Pulse duration, CAS low, CAS-before RAS refresh	6.5t <sub>Q</sub> - 25		6.5t <sub>Q</sub> - 10		ns
158	<sup>t</sup> su(CH-RL)	Setup time of CAS high to RASI, CAS-before-RAS refresh	3.5t <sub>Q</sub> 15		3.5t <sub>Q</sub> - 10		ns

<sup>&</sup>lt;sup>1</sup>These values are derived from characterization and are not tested.

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# CAS-before-RAS DRAM refresh cycle timing



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## local bus timing parameters (continued)

Quarter clock time  $t_Q$ , which appears in the following table, is one quarter of a local output clock cycle, or  $2t_C(ICK)$ .

NO.	PARAMETER		TMS34010-40		TMS34010-50 TMS34010-60		UNIT
	İ		MIN	MAX	MIN	MAX	7
159	¹h(CK2H-RH)	Hold time of RAS high after LCLK2 high, all cycles except internal and CAS-before-RAS refresh	t <sub>Q</sub> 15		tQ - 10	)	ns
160	isu(RL CK2L)	Setup time of RAS low to LCLK21, all cycles except internal and CAS before-RAS refresh	t <sub>Q</sub> – 20		t <sub>Q</sub> - 10	)	ns
161	<sup>†</sup> h(CK1L-RH)	Hold time of RAS high after LCLK1 low, CAS-before-RAS refresh	t <sub>Q</sub> – 15		t <sub>Q</sub> - 10	)	ns
162	¹su(RL-CK1H)	Setup time of RAS low to LCLK11, CAS-before RAS refresh	t <sub>Q</sub> - 20		t <sub>Q</sub> - 10	)	ns
163	th(CK1L-RL)	Hold time of RAS low after LCLK1 low, all cycles except internal	t <sub>Q</sub> - 15		t <sub>Q</sub> 10	<b>)</b>	กร
164	tsu(RH CK1H)	Setup time of RAS high to LCLK1*, all cycles except internal	t <sub>Q</sub> - 20		t <sub>Q</sub> - 10	)	ns
165	<sup>1</sup> h(CK2L-ALH)	Hold time of $\overline{\text{LAL}}$ high after LCLK2 low, all cycles except internal	0.5t <sub>Q</sub> - 15		0.5t <sub>Q</sub> - 10	)	ns
166	t <sub>su(ALL-CK1H)</sub>	Setup time of TAL low to LCLK11, all cycles except internal	0.5t <sub>Q</sub> – 15		0.5tQ - 10	)	ns
167	<sup>t</sup> h(CK2L-ALL)	Hold time of LAL low after LCLK2 low, all cycles except internal	t <sub>Q</sub> – 15		t <sub>Q</sub> - 10	)	ns
168	t <sub>su(ALH-CK2H)</sub>	Setup time of TAT high to LCLK21, all cycles except internal	t <sub>Q</sub> 20		t <sub>Q</sub> 10	)	ns
169	th(CK1H-CH)	Hold time of CAS high after ECLK1 high, CAS-before RAS refresh	t <sub>Q</sub> - 15		t <sub>Q</sub> - 10	)	ns
170	tsu(CL-CK1L)	Setup time of CAS low to LCLK11, CAS-before-RAS refresh	t <sub>Q</sub> – 20		t <sub>Ω</sub> - 10	)	กร
171	th(CK2L-CH)	Hold time of CAS high after LCLK2 low, cycles except internal, DRAM refresh and CAS-before-RAS refresh	t <sub>Q</sub> 15		10 - 10	)	ns
172	t <sub>su(CL-CK2H)</sub>	Setup time of CAS low to LCLK21, all cycles except internal, DRAM refresh, and CAS-before-RAS refresh	t <sub>Q</sub> – 20		t <sub>Q</sub> – 10	)	ns
173	th(CK2L-CL)	Hold time of CAS low after LCLK2 low, all cycles except internal and DRAM refresh	0.5t <sub>Q</sub> - 15		0.5t <sub>Q</sub> - 10	)	ns
174	t <sub>su(CH-CK1H)</sub>	Setup time of CAS high to LCLK11, all cycles except internal and DRAM refresh	0.5t <sub>Q</sub> - 15		0.5t <sub>Q</sub> = 10	)	ns
175	in(CK1H-WH)TR	Hold time of $\overline{W}$ high after LCLK1 high, shift register transfer	t <sub>Q</sub> 15		t <u>a</u> - 10	)	ns
176	t <sub>su</sub> (WL-CK1L)TR	Setup time of $\overline{W}$ low to LCLK11, shift register transfer	t <sub>Q</sub> - 20		t <sub>Q</sub> - 10	)	ns

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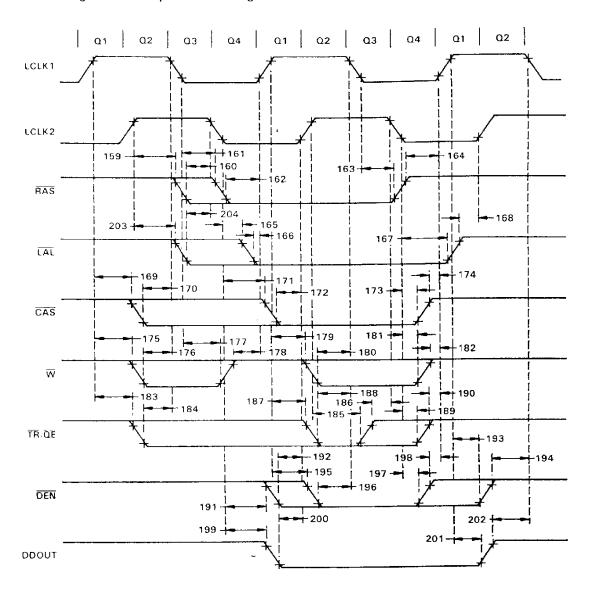
## local bus timing parameters (concluded)

Quarter clock time  $t_Q$ , which appears in the following table, is one quarter of a local output clock cycle, or  $2t_C(ICK)$ .

NO.	PARAMETER		TMS340	10-40	TMS34		UNIT
			MIN	MAX	MIN	MAX	Ī
177	th(CK11-WL)	Hold time of $\overline{\mathbf{W}}$ low after LCLK1 low, shift register transfer	t <sub>Q</sub> – 15		t <sub>Q</sub> - 10		ns
: 78	su,WH-CK1H)	Setup time of $\overline{W}$ high to LCLK1!, shift register transfer	t <sub>Q</sub> − 20		t <sub>Q</sub> - 10		ns
179	inckih-wh)	Hold time of ₩ high after LCLK1 high, write	t <sub>Q</sub> - 15		t <sub>Q</sub> - 10		ns
180	¹su(WL-CK1L)	Setup time of $\overline{\mathbb{W}}$ low to LCLK11, write	t <sub>Q</sub> - 20		t <sub>Q</sub> - 10		ns
181	th(CK2L-WL)	Hold time of W low after LCLK2 low, write	0.5t <sub>Q</sub> - 15		0.5t <sub>Q</sub> - 10	-	ns
182	su(WH-CK1H)	Setup time of W high to LCLK11, write	0.5t <sub>Q</sub> - 15		0.5t <sub>Q</sub> - 10		ns
183	<sup>‡</sup> h(CK1L-TRH)	Hold time of $\overline{TR}/\overline{QE}$ high after LCLK1 high, shift register transfer	t <sub>Q</sub> – 15		t <sub>Q</sub> - 10		ns
184	<sup>1</sup> su(TRL-CK1H)	Setup time of TR/QE low to LCLK11, shift register transfer	t <sub>Q</sub> – 20		t <sub>Q</sub> – 10		ns
185	<sup>t</sup> h(CK2H-TRL)	Hold time of TR/QE low after LCLK2 high, shift register transfer	t <sub>Q</sub> – 15	- 1144	t <sub>Q</sub> - 10		ns
186	t <sub>su(TRH-</sub> CK2L)	Setup time of TR/OE high to LCLK21, shift register transfer	t <sub>Q</sub> - 20	<u> </u>	t <sub>Q</sub> 10		ns
187	(h,CK1H-QEH)	Hold time of TR/QE high after LCLK1 high, read	t <sub>Q</sub> – 15		t <sub>Q</sub> - 10	•	ns
198	IsurQEL-CK1L)	Setup time of TR/QE low to LCLK1., read	t <sub>Q</sub> - 20		t <sub>Q</sub> - 10		ns
189	th(CK2L QEL)	Hold time of $\overline{TR}/\overline{QE}$ low after LCLK2 low, read	0.5t <sub>Q</sub> - 15		0.5t <sub>Q</sub> - 10		ns
190	tsutQEH-CK1H)	Setup time of TR/QE high to LCLK11, read	0.5t <sub>Q</sub> - 15		0.5t <sub>Q</sub> 10		ns
191	th(CK2L-ENH)	Hold time of DEN high after LCLK2 low, write	ta 15		t <sub>Q</sub> - 10		ns
192	tsutENL-CK2H)	Setup time of DEN low to LCLK21, read	t <sub>Q</sub> - 20		t <sub>Q</sub> - 10		ns
193	<sup>1</sup> h(CK1H-ENL)	Hold time of DEN low after LCLK1 high, write	t <sub>Q</sub> – 15		t <sub>Q</sub> - 10		ns
194	†sutENH-CK1L)	Setup time of DEN high to LCLK11, write	t <sub>Q</sub> - 20	-	t <sub>Q</sub> - 10		ns
195	In(CK1H-ENH)	Hold time of DEN high after LCLK1 high, read	tQ - 15		t <sub>Q</sub> - 10		ns
196	<sup>1</sup> su(ENL-CK1L)	Setup time of DEN low to LCLK1;, read	10 - 20		t <sub>Q</sub> - 10		ns
97	thiCK2L-ENLI	Hold time of DEN low after LCLK2 low, read	0.5t <sub>Q</sub> - 15		0.5t <sub>Q</sub> = 10		ns
.38	i <sup>3</sup> su(ENH-CK1H)	Setup time of DEN high to LCLK11, read	0.5t <sub>Q</sub> - 15		0.5t <sub>O</sub> 10		ns
129	In CK2L-DDHI	Hold time of DDOUT high after LCLK2 low, read	to 15		t <sub>Q</sub> - 10		ns
300	(su(DDL-CK2H)	Setup time of DDOUT low to LCLK21, read	t <sub>Q</sub> – 20		t <sub>Q</sub> 10		ns
201	<sup>ក្</sup> ក(CK1H-DDL)	Hold time of DDOUT low after LCLK1 high, read	t <sub>Q</sub> – 15		t <sub>Q</sub> - 10		ns
202	<sup>T</sup> suIDDH-CK1LI	Setup time of DDOUT high to LCLK11, read	t <sub>Q</sub> - 20		t <sub>Q</sub> - 10		ns
203	<sup>‡</sup> h(CK2H-ALH)	Hold time of LAL high after LCLK2 high, CAS-before-RAS refresh	t <sub>Q</sub> – 15		t <sub>Q</sub> - 10		ns
204	tsu(ALL-CK2L)	Setup time of LAL low to LCLK21, CAS-before-RAS refresh	t <sub>Q</sub> - 20		t <sub>Q</sub> -10		ns

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local bus timing: relationship of control signals to clocks



#### video interface timing parameters

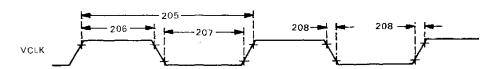
The timing parameters for TMS34010 video interface signals are shown in the next three tables and diagrams. The video interface includes the following TMS34010 pins: VCLK (video input clock), BLANK (blanking), HSYNC (horizontal sync, bidirectional), and VSYNC (vertical sync, bidirectional). HSYNC and VSYNC are inputs if external sync mode is enabled; otherwise they are outputs.

#### video input clock timing parameters

NO.		PARAMETER	TM\$34010-40	TMS34010-50 TMS34010-60	UNIT
			MIN MAX	MIN MAX	L
205	: latVCKI	Period of video input clock VCLK	100	80	ns
206	TWIVCKHI	Pulse duration of VCLK high	40	30	ns
207	*WIVCKL)	Pulse duration of VCLK low	40	30	ns
208	Ti(VCK)	Transition time (rise and fall) of VCLK	51	5 <sup>†</sup>	ns

This value is determined through computer simulation and is not tested.

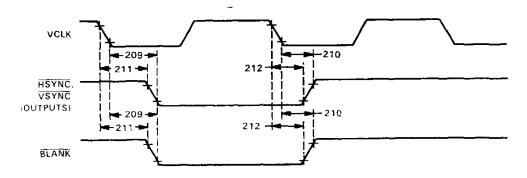
#### video input clock timing



#### video interface timing parameters: outputs

NO.	PARAMETER	TMS34010-40	TMS34010-50 TMS34010-60	UNIT
		MIN MAX	MIN MAX	
209	tu(VCKL-HSL) Delay from VCLK low to HSYNC, VSYNC, or BLANK low	30	30	ns
210	Tolveke-HSH) Delay from VCLK low to HSYNC, VSYNC, or BLANK high	30	30	ns
2 1 1	Invocklinsh; Hold time of HSYNC, VSYNC, or BLANK high after VCLKI	0	0	ns
212	THIVOKE-HSL) Hold time of HSYNC, VSYNC, or BLANK low after VCLK1	0	0	ns

#### video output timing



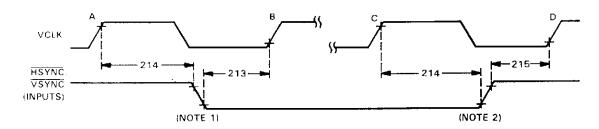
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#### video interface timing: external sync inputs

NO.	PARAMETER	TMS34010-40	TMS34010-50 TMS34010-60	UNIT
		MIN MAX	MIN MAX	
213	tsu(HSV_VCKH) Setup time of HSYNC, VSYNC valid to VCLK1	20 <sup>†</sup>	20 <sup>†</sup>	ns
214	th(VCKH-HSV) Hold time of HSYNC, VSYNC valid after VCLK high	20†	20 <sup>†</sup>	пs
, 115	*sutHSH-VCKH) Setup time of HSYNC, VSYNC high to VCLK1	20 <sup>‡</sup>	20‡	пs

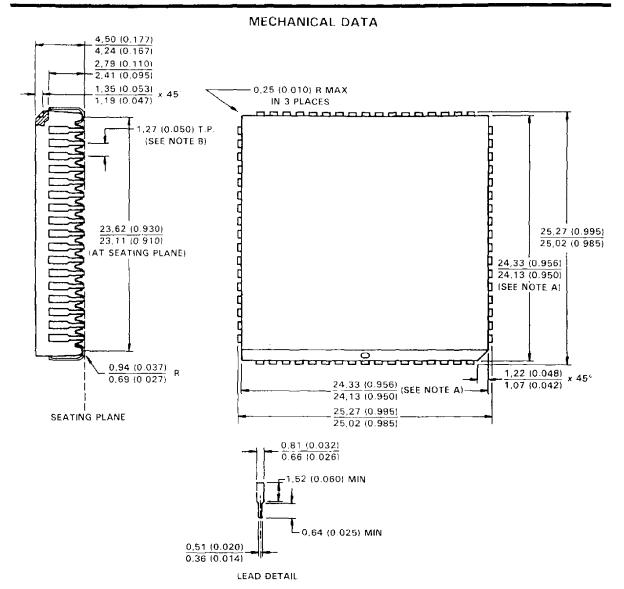
Specified setup and hold times on asynchronous inputs are required only to guarantee recognition at indicated clock edge.

#### external sync input timing



- NOTES 1 If the falling edge of the sync signal occurs more than th(SV-VCH) past VCLK edge A, and at least t<sub>su(SV-VCH)</sub> before edge B, the transition will be detected at edge B instead of edge A.
  - 2 If the rising edge of the sync signal occurs more than th(SV-VCH) past VCLK edge C, and at least t<sub>su</sub>(SV-VCH) before edge D, the transition will be detected at edge D instead of edge C.

 $<sup>1.7 \, \</sup>mathrm{ft}$  s value is determined through computer simulation.



NOTES A Centerine of center pin each side is within 0.10 (0.004) of package centerline as determined by this dimension. B Location of each pin is within 0.127 (0.005) of true position with respect to center pin on each side

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